

EXPLORING ANALOG AND DIGITAL DESIGN USING THE
OPEN-SOURCE ELECTRIC VLSI DESIGN SYSTEM

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The design of VLSI electronic circuits can be achieved at many different abstraction levels starting from system behavior to the most detailed, physical layout level. As the number of transistors in VLSI circuits is increasing, the complexity of the design is also increasing, and it is now beyond human ability to manage. Hence CAD (Computer Aided design) or EDA (Electronic Design Automation) tools are involved in the design. EDA or CAD tools automate the design, verification and testing of these VLSI circuits. In today's market, there are many EDA tools available. However, they are very expensive and require high-performance platforms. One of the key challenges today is to select appropriate CAD or EDA tools which are open-source for academic purposes. This thesis provides a detailed examination of an open-source EDA tool called Electric VLSI Design system. An excellent and efficient CAD tool useful for students and teachers to implement ideas by modifying the source code, Electric fulfills these requirements. This thesis' primary objective is to explain the Electric software features and architecture and to provide various digital and analog designs that are implemented by this software for educational purposes. Since the choice of an EDA tool is based on the efficiency and functions that it can provide, this thesis explains all the analysis and synthesis tools that electric provides and how efficient they are. Hence, this thesis is of benefit for students and teachers that choose Electric as their open-source EDA tool for educational purposes.

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CHAPTER 1

INTRODUCTION

Electronic systems play a crucial role in human life. Electronic systems ranging from Integrated Circuits (ICs) to PCB (Printed Circuit Boards) are developed and produced by EDA (Electronic Design Automation) tools. EDA is a collection of algorithms, methodologies, and tools which automate the design, verification and testing of electronic systems. There are many commercial EDA tools, which are the industry standard and very expensive to license such as Cadence, Mentor Graphics, Synopsys, etc. Free/Open-Source Software (FOSS) EDA tools are the only effective way for students and teachers to learn and implement their ideas by modifying the source code. The Electric VLSI Design System is a sophisticated open-source CAD system which can handle a variety of technologies such as CMOS and Bipolar from schematics to the layout. It has many generic analysis and synthesis tools which can automate the design and reduce the time and work. It also supports most popular interchange and manufacturing formats such as EDIF, VHDL, GDS, LEF/DEF, etc. [6, 35, 19].

Figure 1.1 shows the various VLSI design abstraction levels [19, 20]. Hardware designers use these VLSI design abstraction levels to ensure that all the sets of specifications and primary goals such as power consumption, speed, etc. are met. With the given set of specifications, the main objective at the system level is to define the partitions of the system and their interfaces. The next step is to represent the subsystem's behavior using high-level programming languages. Through behavioral verification, we could know whether the model has met the requirements or not. After the specifications are assured, the next step in the design process is to define the design at Register Transfer Level (RTL) [23]. At RTL, the timing and data transfers between simple functional units such as registers, full-adders, decoders, counters, etc. are described. At gate level, the design is a structure of gates, latches, and flip-flops. In this level, the accurate area and delay are estimated [21]. In transistor or circuit level, the design is implemented with transistors. Physical design plays a most vital

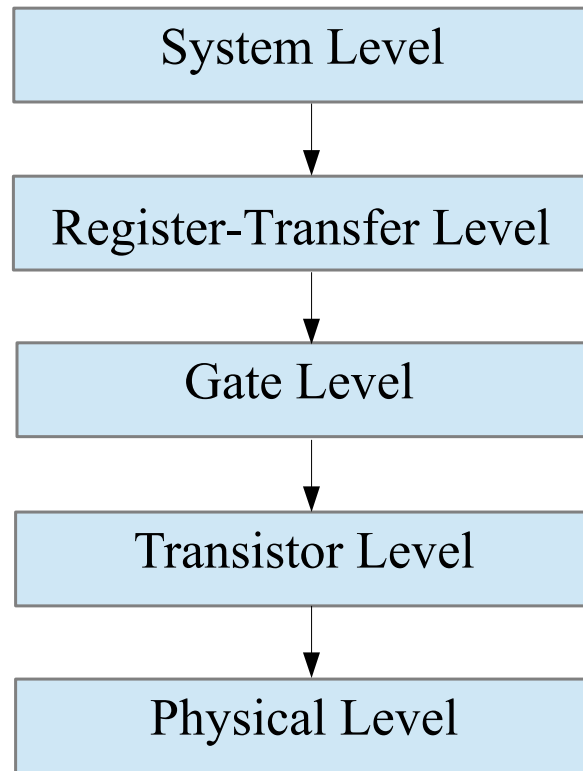


FIGURE 1.1. VLSI Design Abstraction Levels

role in the design steps because it deals with the area, power and performance of the final electronic system or circuit. It also completes the floorplanning, placement, and routing for the design [37]. The designer can use the Electric software from gate level to physical level design of an IC design flow. Since it does not have an inbuilt Verilog simulator, it can't simulate Verilog code, but it can build Verilog decks for simulation in different Verilog simulators.

1.1. Existing Open-Source EDA Tools

Based on the VLSI design flow, a good EDA tool should support features such as logical design, circuit schematics, layout generation, and also design rule check. In today's market, most VLSI CAD systems which support all these features are not FOSS, but there are some open source tools which support some features individually. These are listed in table 1.1 [19]. The main drawback of other open-source EDA tools is that they are not

as comprehensive as Electric. Even though some tools support some features the totality of features is not integrated into one CAD system which is FOSS. Only the Electric CAD system supports all desired features and is comprehensive [34].

Tools	Version	Licence	Supported Platform	Funtions
Electric	Version 9.06	GPL	Mac OS, Windows, Linux	HDL to Layout, Mixed-Signal
Toped	Toped 0.9.8	GPL	Windows, Linux	Circuit Layout, Mixed-Signal
gEDA	version 1.8.2	GPL	Linux, Mac OS X	PCB Design, Schematics
Magic	Magic 8.1	BSD	Linux	Circuit Layout, Mixed-Signal
eSim	Version 1.0.0	GPL	Windows, Linux	PCB Design, Schematics
Xcircuit	Version 3.9	GPL	Windows, Unix	Schematic Capture
Qucs	Release 0.0.18	GPL	Mac OS, Windows, Linux	PCB Design, Schematics

TABLE 1.1. Existing Open Source EDA tools

1.2. Organization of the Thesis

This thesis is organized as follows.

Chapter 2 explains the history, architecture, features and also installation of the Electric VLSI Design system. Design environments, analysis and synthesis tools and also external interfaces that are provided by Electric are described here.

Chapter 3 presents four digital designs that are implemented with Electric. The accuracy of the simulations and layout designs of digital circuits demonstrates how electric can handle digital design.

Chapter 4 presents four analog designs that are implemented with Electric. This chapter also demonstrates how Electric can handle analog layout design and simulation.

Chapter 5 discusses directions for future work and conclusions.

CHAPTER 2

THE ELECTRIC VLSI DESIGN SYSTEM: FEATURES AND SOFTWARE ARCHITECTURE

2.1. Electric History

Initially, the Electric VLSI design system was written in the C language in 1982 by Steven Rubin [35] at the Fairchild A.I. Laboratory in Palo Alto, California. After 2003, it was ported to Java.

- In 1983, the first paper about Electric was published. It was available to universities in source-code form.
- In the mid 1980s, Electric was commercially released by Applicon with the name Bravo3VLSI.
- In 1988, a company called Electric Editor Incorporated was founded and sold Electric commercially.
- In 1998, “Electric Editor Incorporated” stepped forward and gave the Electric source code to the Free Software Foundation (FSF). The FSF is the primary organizational sponsor for the GNU Operating System, and its aim is to promote computer user freedom and give everyone equal rights to their programs.
- In 2000, Steven Rubin created Static Free Software, which developed and maintained Electric.
- In 2004, Static Free Software become part of RuLabinsky Enterprises, Inc. and continued developing Electric as free software.
- In June 2005, the Java version of Electric has released after abandoning the C version in September 2003. It took two years to complete the translation. Even now, the C version is still available on the site.
- In 2010, Oracle acquired Sun Microsystems and Electric. It continued the Electric development and still makes it available as free software.

Electric was built because there were no design systems that had a combination of graphics, connectivity, and accurate geometry for IC design. The Electric design system has a vast database which is built on network structure, primarily to implement connectivity. The network has nodes and arcs, which are components in the circuit and connecting wires respectively. These network nodes and arcs have their own geometric data, for a correct representation of the circuit. Electric has an expansive database and can store a large number of structures, design rules, etc.

2.2. Electric Installation

2.2.1. Downloading Electric

The Electric software is simply a JAR file. JAR or Java Archive is a file format which aggregates many Java class files and associated images, text, etc. into one single archive file. There are three ways to run the Electric software [13].

2.2.1.1. Run from the web

Running from the web is the easiest way to try. The user has to download a Java Web Start file from the link available [33]. This file has links to the Electric, and whenever there is a new release of the software, it automatically downloads it to the system. It is slow at first because it downloads the additional files to the system.

2.2.1.2. Download the JAR file

Since Electric software is a jar file, it doesn't require installation. It doesn't require tedious commands or other third party resources files to run it. The latest version of Electric available is 9.06, and it is called "Electric-9.06.jar". There are two versions of JAR files available online at the www.staticfreesoft.com site. One is with source code, and another one is without source code. The one with source code is named as "Source" and without the source code is called the "Binary" version.

2.2.1.3. Building Electric from source code

The first thing one has to do for running Electric software from source code is to create an account on java.net. The source code is available at java.net/projects/Electric. Even though the source version of Electric has the source code, it is not recommended because it doesn't handle dependencies. The easiest way of downloading the source from the repository is through SVN checkout, with the software TortoiseSVN. TortoiseSVN is a free open-source windows client. After downloading the Electric source code, one has to obtain a java programming IDE (Integrated Development Environment) such as NetBeans or Eclipse.

2.2.2. Supported Environments

Macintosh (system 7 or higher), UNIX (all Variants), and Windows (XP, 2000, 8, 10). This flexibility alone makes Electric to be chosen among other free open-source IC layout software.

2.2.3. System Requirements

Electric can be run even on low-end systems but it requires Apache Harmony, OpenJDK or Oracle Java Version 1.6 or higher to be installed on the system. Since Electric is written in Java and Oracle supports it, it is recommended to install Java 1.6 or higher versions on the system.

2.2.3.1. Memory Control

The only known problem with Java is that the Java Virtual Machine (JVM) limits the programs from growing too large. Since it has a memory limit, very large circuits in Electric can't be edited. The Electric software has a solution for this issue. Electric can request more memory from the Java whenever it runs out of memory. For windows, one can set the maximum memory to 1.5 Gigabytes. For Linux and Macintosh, it can exceed 3.6 Gigabytes.

2.2.4. Plugins

Electric can handle external sources or Java plugins to extend its functionalities. GNU does not distribute these plugins because of copyright restrictions. These plugins must be downloaded separately. If Electric is built from the source code, all plugins are available and this is the easiest way to obtain the plugins.

- **Jython:** Jython is a Java package which implements Python language scripts on the Java Platform. Python source code is compiled down to Java bytecodes by the compiler in Jython. These Java bytecodes can run directly on the JVM which needs a set of libraries to compile and Jython supports them. Jython can be download from the www.Jython.org.
- **Bean Shell:** Bean shell is also a Java package which evaluates Java expressions and scripts. Bean shell can be embedded into the Java platform and can run Java syntax and scripts with a set of libraries. It can be downloaded from www.beanshell.org.
- **IRSIM:** IRSIM is a switch level simulator for digital circuits from Stanford University. It was originally written in the C language, and then was translated to Java so it could plug into Electric. It is available from www.staticfreesoft.com.
- **Java3D:** Java 3D is not a plugin; rather it is a Java package. After installing Java3D, Electric can integrate it functionalities into the software. It facilitates one to view the physical design in three dimensions. It can help the designer to see the connections between the nodes and contacts. It also helps students to learn from the 3D view of the layout diagram. It is available from the site www.j3d.org.
- **Java Media Framework:** Java Media Framework (JMF) is an enhancement to Java. It adds extra facilities to Java3D and animates the 3D capture. It is available from Oracle.

2.2.5. Source Code

The source code can be downloaded from the repository. A typical Java source code contains packages, interfaces, fields, classes, methods, etc. A package is a namespace that

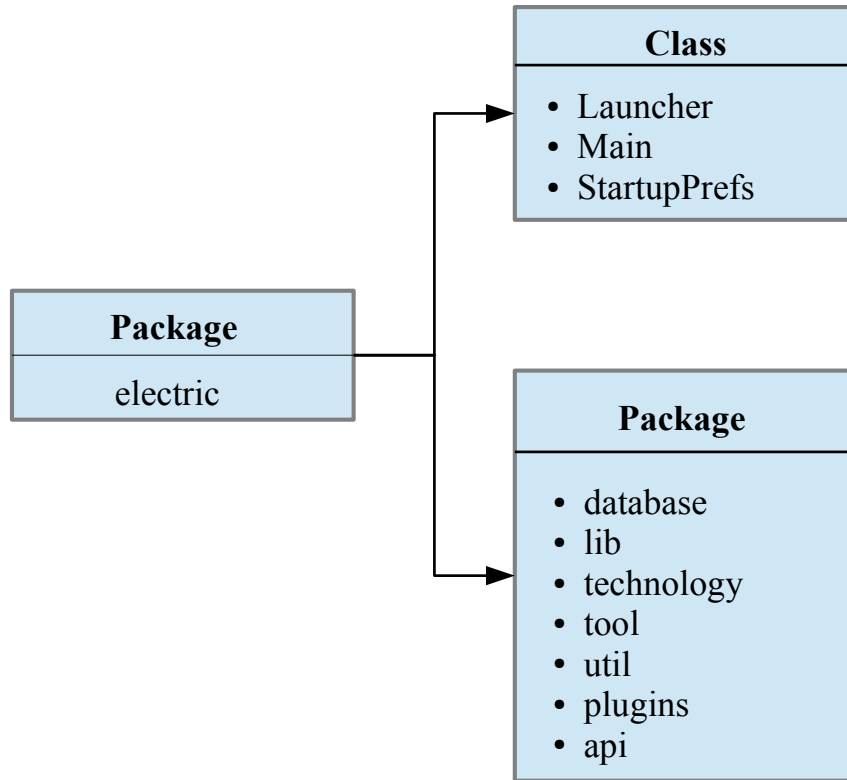


FIGURE 2.1. Block diagram of Electric Source Code

organizes a set of related classes and interfaces. Typically a package is similar to different folders on the computer. After downloading the Electric source code, the source code starts from the package name com, then sun, and then the actual Electric package which contains all the packages required to build Electric. The Electric package is shown in the block diagram shown in figure 2.1. It contains three classes and seven other packages. The class launcher initializes the Electric software, the Main class initializes Electric and then starts the system. StartupPrefs is a module to access preferences which are used in starting the Electric software. Table 2.1 shows the list of packages that are essential for programming and can also be useful for modifying the code to implement new concepts in Electric.

Package	Description
com.sun.Electric	It has all the packages to build Electric.
com.sun.Electric.database	This package handles the database for Electric.
com.sun.Electric.lib	It has all the built-in library files.
com.sun.Electric.technology	It has all technology information for Electric.
com.sun.Electric.tool	Package for all analysis and synthesis tools.
com.sun.Electric.util	Package for all utilities.
com.sun.Electric.Plugins	It has all plugin information for Electric.
com.sun.Electric.api	Package for all Application programming Interfaces.
com.sun.Electric.database.geometry	Package for geometric support in Electric.
com.sun.Electric.database.hierarchy	Package for hierarchy (cell instances inside of cells).
com.sun.Electric.database.prototype	Package for the prototype classes in Electric.
com.sun.Electric.database.topology	Package for connected Nodes and Arcs.

TABLE 2.1. List of Fundamental Packages in the Electric source code.

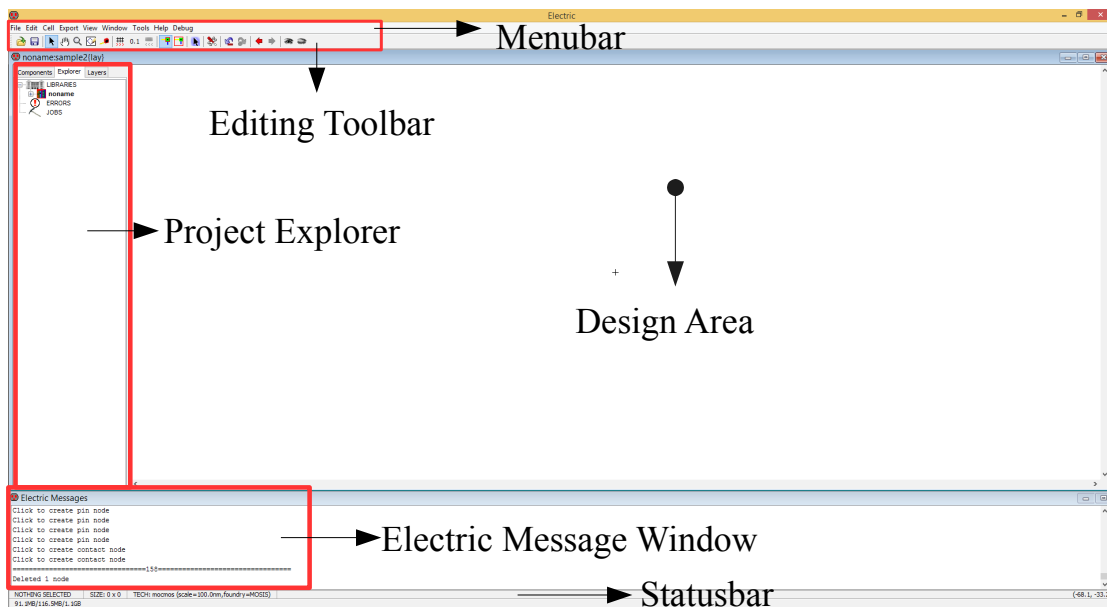


FIGURE 2.2. Electric Main GUI

2.3. Electric Features

2.3.1. Electric GUI

The Electric GUI (figure 2.2) consists of Menubar, Editing Toolbar, Status bar, Project Explorer, and the Electric Messages window. Menubar of the Electric consists of all the menus such as File, Edit, Cell, Export, View, Window, Tools, Help, Debug. The File menu provides important options for creating a new library, open existing library, importing and exporting modern interchange and manufacturing format, and saving the library. The Edit menu contains all the editing commands needed for editing the current library or cell. It also provides additional options such as technology editing and technology specific options, where technology editing includes technology creation wizard where one can edit the design rules for any particular technology and technology specific option includes describing the current technology for the designers. The Cell menu has options to create, edit, copy cells and it also allows designers to move up and down the hierarchy of a cell. The Export menu contains options to export the nodes and pins for the cell to a name, which is decided by designers. The View menu provides designers for editing layout view, or make an icon view of a circuit. The Window menu provides the designer with zooming in or out options and also when the 3D plugin is installed in Electric it gives the designer the ability to view the circuit in three dimensions. The Tools menu provides many analysis and synthesis tools that are integrated into Electric. The Help menu helps the designer in providing the sample library and also general information about Electric.

The Editing Toolbar allows the designer to save, open, zoom-in, zoom-out, increase and decrease the scale functions. Project Explorer window has three other tabs: Components, Explorer, and Layer. Components tab has all the components for each design environment that are required to design a circuit. For example, it has schematic components for designing a schematic level circuit, and it has layout components for designing the layout of a circuit. The Explorer tab shows the project libraries, cells in the libraries and also cells in lower hierarchy. The Layers tab provides options to the designer to make the layers visible, invisible, or select them all for every design environment in Electric. The Electric

message window shows the result of current and previous actions. For example, if a DRC check has been done on a circuit, the result whether it passed or failed is shown in this window. The Status bar has three parts: the first part displays the name of the component selected, the second part displays the size of the design, the third part shows the current design environment of the cell and also shows the scale.

2.3.2. Representation

Any graphical CAD system can offer two basic user-interface styles, connectivity, and geometry. The connectivity approach is used by all schematic capture based systems: components are placed, and wires are used to connect them. As the system already knows that the wires connect to the components, the circuit is properly connected, even when they are moved. Integrated circuit layout systems use the geometry approach. Masks for chip fabrication are formed by different layers, which are laid in areas of “paint”. The connectivity is absolutely not present, and any of the pieces of paint can vary the circuit’s topology [28]. For any connectivity information, one has to go through the error-prone “node-extraction” phase. Electric is different because it uses the connectivity approach for even integrated circuit layout. For example, for a PMOS transistor, a designer can place PMOS transistors, contacts, etc. and draw wires such as metal-1, polysilicon-1, etc. to connect them. This connectivity-based approach shows the geometry and also the connectivity between them. Electric uses the terms **nodes** and **arcs** for the components and wires respectively. For a detailed explanation, a node is a component in the design environment of Electric and an arc is a connecting wire and it’s more than that in Electric. They can be made into many forms with respect to the design environment. Even when the circuit is changed, the arc remains connected. It is the most important property of arc in Electric. Figure 2.3 shows the representation of nodes and arcs. A transistor node, poly arc, and a contact node are shown. Nodes always have ports on them, which are the connection sites for an arc. An arc always connects to two nodes [2].

Integrated circuit layout tools available in the market are polygon-based or paint-based tools, whereas Electric is a connectivity based layout tool. Figure 2.4 shows the shows

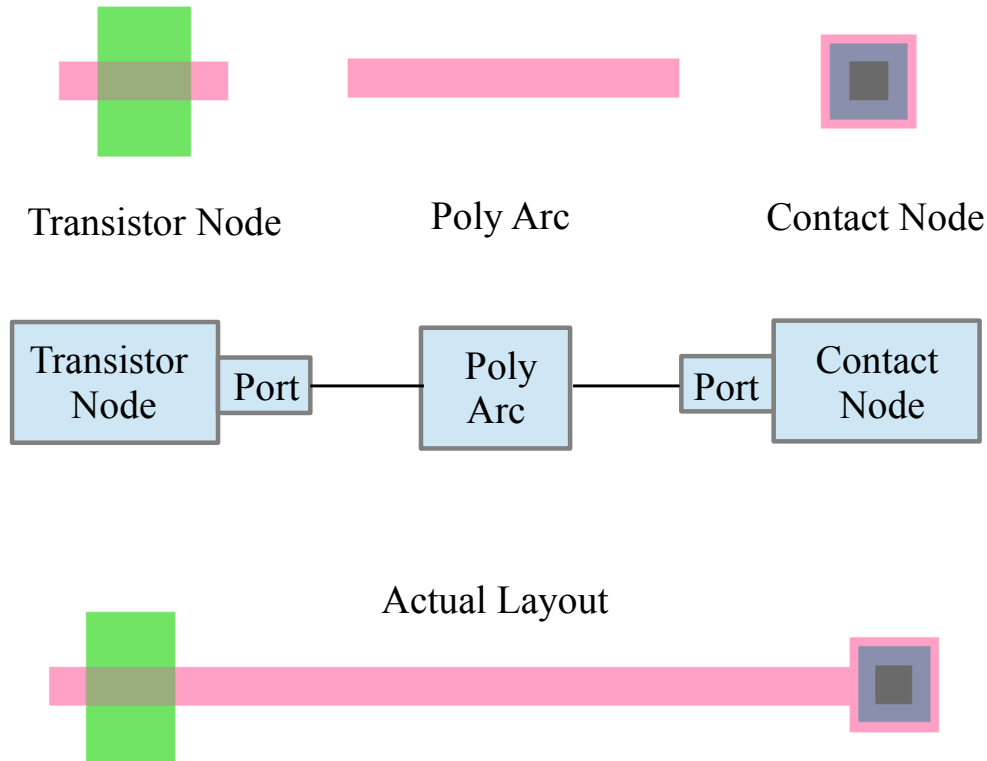
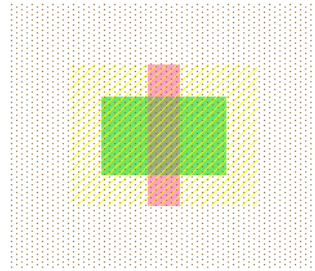
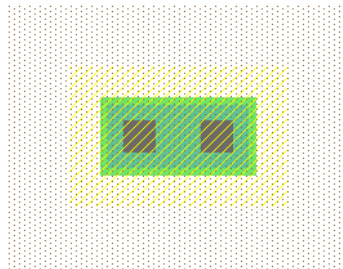


FIGURE 2.3. Representation in the Electric tool.

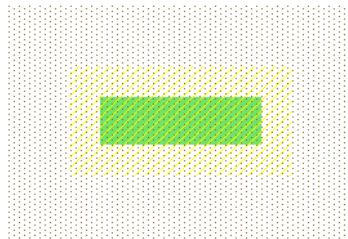
the nodes and arcs required to build a PMOS transistor in Electric. Figure 2.5 shows the layers needed to form a PMOS transistor and also the actual layout of a PMOS transistor in polygon based tools. In polygon-based integrated circuit layout tools, six different layers are required to form a PMOS transistor. In Electric, a PMOS transistor node itself has N-well, Active, p-select, and poly layers as per design rules. These layers expand when one changes the width and length of a node. In a similar way, a P-Active contact has N-well, P-select, Active, metal-1, and contact layers in it. Even these expand when the designer changes the length and width. P-active also consists of N-well, P-select, Active layers in it. Whenever there is a need to alter the size of a transistor, a designer just needs to change the length and width of these components. Hence, there is no need to redraw the layers, and also, there will be fewer geometrical errors.



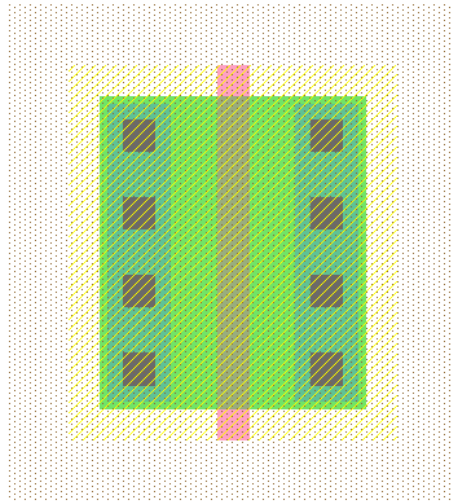
PMOS transistor Node



P-Active Contact



P-Active Arc

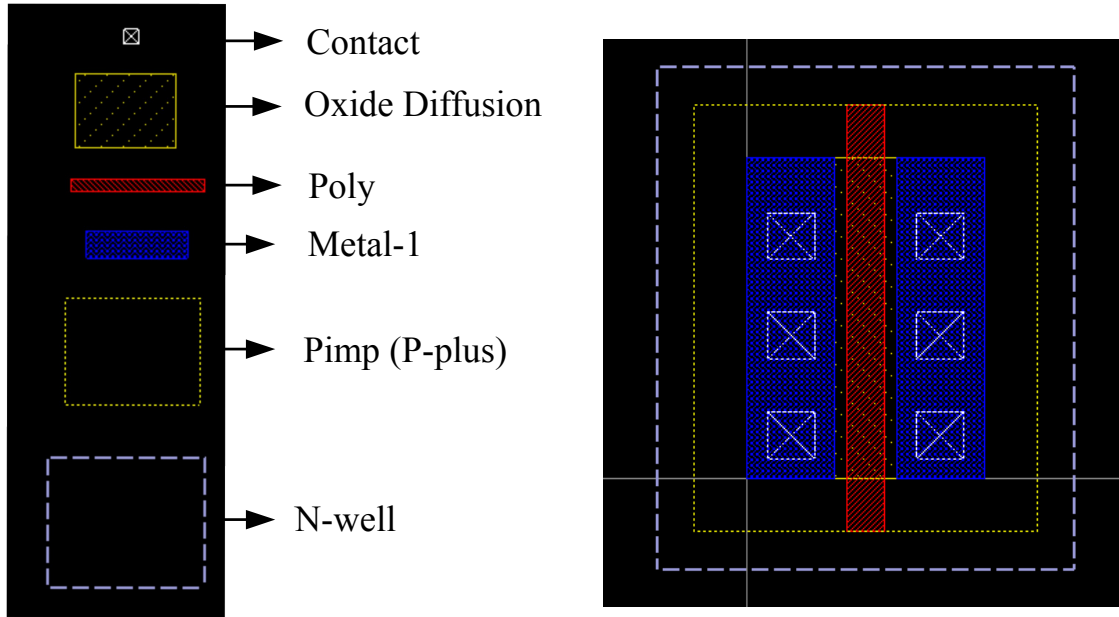


(a) Nodes and Arcs of PMOS transistor. (b) PMOS transistor in Electric tool.

FIGURE 2.4. PMOS transistor and its components in Electric tool.

2.3.3. Design Environments

Electric provides many different design environments. These environments exist as a **technology** in Electric. Every design environment consists of a set of primitive nodes, arcs and also has some information about design rules. Most of these environments are for the layout of integrated circuits, and also, non-IC design environments are present in Electric. This thesis mainly concentrates on CMOS technology. In Electric, technologies are in XML



(a) PMOS transistor layers.

(b) PMOS transistor in polygon based tool.

FIGURE 2.5. PMOS transistor and its layers in polygon-based tool.

format, which contains physical and Electrical details of the foundry process, and they are attached to the layers which include the design rules, etc. These is Electric-independent information. It also contains Electric specific information such as primitive nodes and arcs for designing in Electric. These XML files are automatically generated by Electric by using the **Technology editor** and **Technology- creation Wizard** in **Edit** menu. Electric allows the designer to edit the technology by converting the current technology into libraries by using the command **Convert technology to library for editing** in **Edit/ technology editing** menu. The design environments that are provided by Electric are shown in table 2.2 [28].

2.3.4. Analysis and Synthesis Tools

Since VLSI design has become more complex and very hard to complete the whole design by hand, there is a need for analysis and synthesis tools. Synthesis tools will create or generate circuitry automatically, and analysis tools will verify the circuitry that has

Design Environment	Description
Artwork	This design environment provides the components that are used for drawing graphics and also creating icons for the cell.
BiCMOS	It is a semiconductor technology which integrates two separate technologies such as bipolar junction transistor and the CMOS transistor in an IC.
Bipolar	It is a bipolar technology (self-aligned and single poly).
CMOS	CMOS is technology, based on an old paper by Griswold Thomas and it was never got into the actual process which exists as an illustration.
FPGA	FPGA (Field programmable gate array) is an IC technology in Electric however it is a basic technology which doesn't have capabilities of FPGA. It has to be customized by the user with architecture file.
Gem	Gem tool is a temporal logic technology in Electric. It is based on the paper by Lansky A.L and Owicki S.S
MOCMOS	It is a CMOS technology that is fabricated by MOSIS project. It has MOSIS design rules which are similar to lambda rules.
RCMOS	RCMOS is the round CMOS technology by Caltech which is an design environment in Electric.
NMOS	It is a technology which uses the only nmos for logic gates and other digital circuits.
PCB	In PCB, Electrical components are connected by conductive tracks, pads etc which are mechanically supported. Electric's PCB technology is very basic and have 8 layers.
Schematic	schematic is a design environment where digital and analog schematic level designs are designed.

TABLE 2.2. Design Environments in Electric.

been designed by hand. Electric comes with many tools which make designing easy for the user. Analysis tools in Electric are DRC, simulators, and network comparison (LVS) tools. Synthesis tools in Electric are circuit generators, Routers, etc. To obtain a list of tools in Electric, the command **List Tools** in the **Tools** menu shows all the tools, including which are active. The list of tools from the menu is shown in figure 2.6.

The **JOBS** section in cell explorer shows which tools are currently running, and the **ERRORS** section in cell explorer, reports the errors that are generated for the current design. By using **Show Next Error** and **Show Previous Error** commands in menu **Edit/ Selection** , one can browse the errors that are reported in **ERRORS** section.

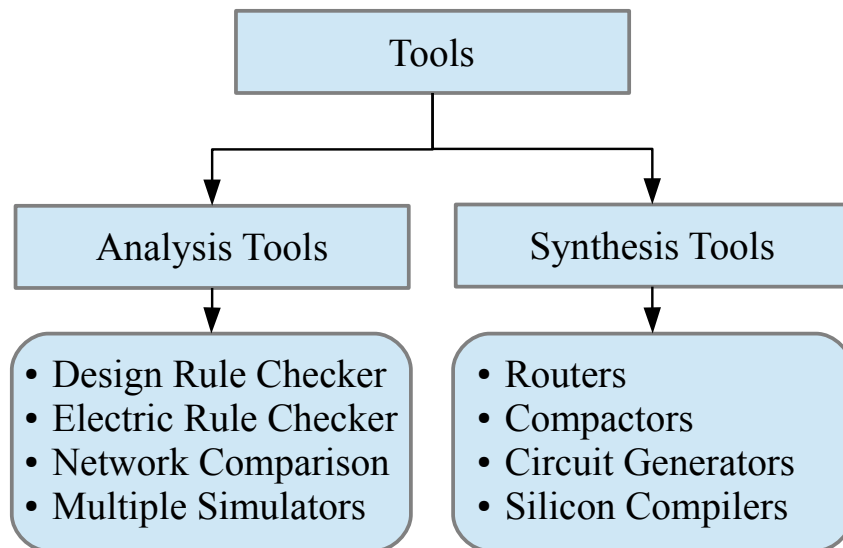


FIGURE 2.6. List of Analysis and synthesis tools.

2.3.4.1. Design Rule Checking

Design rules are necessary for designing any physical level design. These design rules mainly come from the limitations in manufacturing processes [36, 18]. Attempts to reduce defects during mask making or constraints in the precision alignment of photolithography equipment can cause these limitations. The design rule checker ensures that the design is as per the design rules that are given by the technology manufacturer [32, 19]. In Electric, there are three types of design rule checkers: Incremental, Hierarchical and Schematic.

- **Hierarchical DRC:** The Hierarchical design rule checker checks the current cell design and also the hierarchical design of it. The design rules are already present in the Electric software for every technology; there is no need to import the Design rules into Electric. **Check Hierarchically** command in **Tools/DRC** menu checks the hierarchical design of the current cell. Physical level design rules are shown in figure 2.7.
- **Incremental DRC:** The Incremental design rule checker runs continuously in the background as long as the design is being edited. This checker works only on the physical design level environments such as the mocmos, bicmos, mocmosub, etc., It examines the layout and issues error messages as it goes. This feature is one of the best advantages of Electric. The user can make sure the design is as per the design rules right there, without waiting to finish the design and then run Hierarchical DRC.
- **Schematic DRC:** The schematic design rule checker checks the design in the schematic level. It looks for the nodes whose names are the same as network names in the cell, arcs that end on another arc without connection between them, etc. The same **Check Hierarchically** command in **Tools/DRC** menu checks the design when the current cell is in the schematic design environment.

Electric can also read MentorGraphics[®] Calibre[®] and Cadence[®] Assura[®] DRC output files. With the command **Import Assura DRC Errors for Current Cell** and **Import Calibre DRC Errors for Current Cell** from **Tools/DRC** menu. Figure 2.7

shows the fundamental design rules used to design all the physical designs in mocmos technology

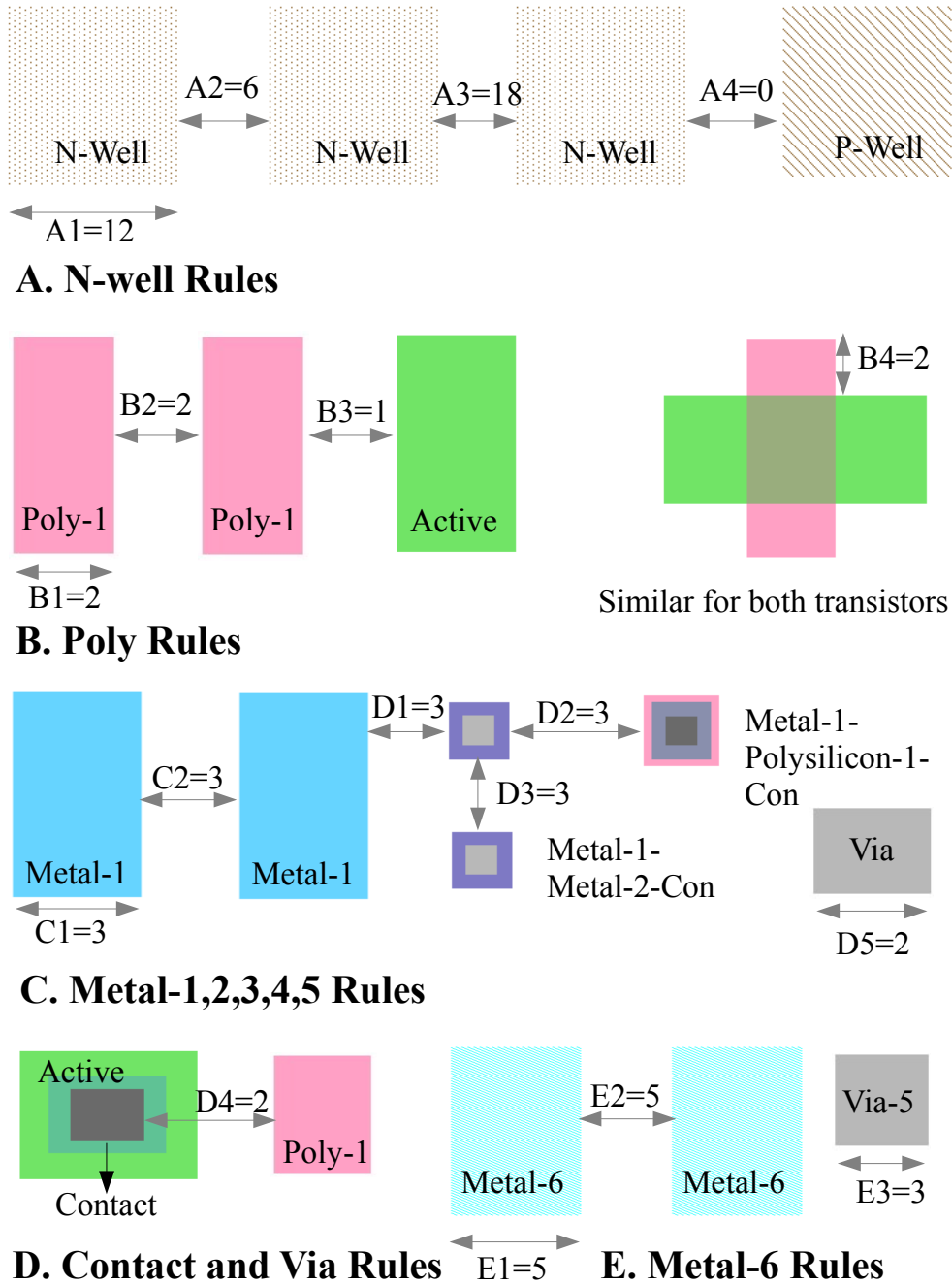


FIGURE 2.7. list of fundamental design rules.

A	N-Well Rules	
A1	Minimum N-well width	12λ
A2	Minimum spacing between wells at same potential	6λ
A3	Minimum spacing between wells at different potential	18λ
A4	Minimum spacing between wells of different type	0
B	Poly Rules	
B1	Polysilicon minimum width	2λ
B2	Minimum spacing over field	3λ
B3	Minimum spacing over active	1λ
B4	Minimum extension over active	2λ
C	Metal-1,2,3,4,5 Rules	
C1	Minimum width of a Metal	3λ
C2	Minimum spacing between metals	3λ
D	Contact and Via-1,2,3,4 Rules	
D1	Minimum distance between contact and metal	3λ
D2	Minimum distance between contacts	3λ
D3	Minimum spacing between contact to poly	2λ
D4	Exact size of a Via	$2X2$
E	Metal-6 and Via-6 Rules	
E1	Minimum width	5λ
E2	Minimum spacing	5λ
E3	Exact size of a via-6	$3X3$

TABLE 2.3. List of fundamental design rules.

2.3.4.2. Electrical Rule Checking

Electric comes with two types of Electric rule checker, Well and Substrate checking and Antenna Rule Checking. The Well Checker checks whether there are well contacts in every area of the well. It also checks whether the power and ground connections are in the appropriate places and checks the spacing rules between well areas. Checking spacing rules can also be done by DRC (Design Rule Checker) after checking the option in the preferences section. The command **Check Wells** in **Tools/ERC** menu will check the wells in the design. Antenna Rule Checker checks the antenna rules for the design. Antenna rules are necessary during fabrication of IC's to make sure that the transistors are not destroyed in that process. In the fabrication process, to form poly and metal layers the wafer is bombarded with ions. These ions should travel to the substrate and active layers through the wafer. If the poly or metal has a large area and if it only connects to gates of the transistor and is not connected to the source and drain, then ions could travel through the transistors. If the ratio between area of poly or metal to the area of the transistor is too large, then the transistors will be destroyed [35]. The command **Antenna Check** in **Tools/ERC** will check the antenna rules for the design [9].

2.3.4.3. Simulation

Electric comes with two built-in simulators, IRSIM and ALS. IRSIM is not available through the Electric jar file due to license restrictions. It is an open-source gate-level simulator created at Stanford university. The easiest way to get the IRSIM simulator is to build Electric software from its source code. Electric can create input decks for Verilog simulation and can also create input decks for spice simulations. The command **Write Verilog Deck** in **Tools/Simulation (Verilog)** menu can produce Verilog decks and the command **Write Spice Deck** in **Tools/Simulation (Spice)** menu can produce spice decks. Electric doesn't have Verilog simulator to simulate the input decks and it only has gate level simulator to simulate the digital designs. One can setup LTspice to simulate the design from Electric. In a similar way HSPICE can also be set up. HSPICE is an industry standard SPICE simulator for over 25 years. It allows accurate circuit simulations which are trusted by many

IC design manufacturers. LTSPICE is a free SPICE simulation software, designed by Linear Technology. It has schematic capture to design the schematic circuits and waveform viewer to analyze the simulation results.

2.3.4.4. Routing

Routing in EDA tools adds wires to components in the design. In Electric there are 4 different types of routers *maze-router*, *river-router*, *sea-of-gates router*, *clock-router* and based on A* and the Lee/Moore algorithms there are 6 experimental routers. From **Tools/Routing** one can choose different types of routing methods [4].

2.3.4.5. Network Consistency Checking

LVS (Layout vs. Schematic) is the tool which checks the layout design to match with the schematic design. In Electric, Network consistency checking (NCC) is used to check two network designs even two layout designs, two schematics designs, layout vs. schematic design, etc. With the command **Schematics and layout views of cell in current window** in the **Tools/NCC** menu one can check the network of both cells. It is one of the important features in Electric, the designer can check anytime and for any cell. [38].

2.3.4.6. Placement

Right placement is necessary for the chip to perform efficiently as it will affect the chip performance and also causes manufacturability problems. In Electric there are different types of algorithms and different types of placement. With the command **Floorplan and Place Current Cell** in **Tools/Placement** menu one can place the current cell using existing algorithms. Force Directed is one of the algorithm that gives good results within seconds. Genetic algorithm is one of the algorithms in Electric for placing that needs long runtimes. These are few types of placement algorithms that are present in Electric.

2.3.4.7. Compaction

The Compaction tool reduces the space between the components to minimal design rule spacing in the layout design. This tool helps the user to make room for many other components in the given area. Electric has not stated the algorithm it uses. It does all single-axis compaction, horizontal and vertical directions until there is no space left in the circuit. **Do compaction** command in **Tools/Compaction** menu will perform the function. [9].

2.3.4.8. Silicon Compiler

Silicon Compiler is a tool which can generate a layout from the user's input VHDL or Verilog code. It was founded by Johannsen, Mead and Cheng in 1981. Though Electric has the tool it has not worked well. It converts VHDL code to the netlist for the QUISC tool. QUISC is a tool that can do place and route of a cell from schematic or structural VHDL description. The command to use the silicon compiler is **Convert Current Cell to Layout** from the **Tools/silicon compiler** menu.

2.3.5. External Interfaces

For compatibility with other EDA systems, Electric supports many popular interchange and manufacturing formats. Importing and exporting the formats can be done using the commands **Import** and **Export** in **File** menu. Many of these formats don't come with circuit connection information. The node extractor in Electric can be used to convert these pure-layer nodes to Electric components.

- **CIF:** CIF is abbreviated as Caltech Intermediate Format and was designed by Caltech. It was originally designed to describe Integrated Circuits. A CIF file consists of textual commands which set layers and draw on them. CIF is old but still in use. The last publication on CIF file format was published on Feb 11, 1980, by the California Institute of Technology.

- **GDS II:** GDS II is an industry standard format for exchange of IC layout artwork. Previously, it was not an open industry standard. It was designed and owned by Calma. Later, it was moved to GE [28]. GDS II file format is the final output for any IC design cycle.
- **DXF:** AutoCAD DXF is abbreviated as Drawing Interchange Format, which is controlled and defined by AutoDesk. It is developed to represent the data used in CAD systems. Almost every type of data can be represented in DXF file format.
- **Verilog and VHDL:** Verilog and VHDL are hardware description languages. Electric can import and export to these languages. Electric has two issues with Verilog; Electric has a weak and old parser which can't handle standard Verilog code. The second problem with Electric is that it can't handle behavioral Verilog. Therefore, it cannot understand some of the Verilog code.
- **Eagle, Pads, ECAD:** Eagle is an interface to CadSoft's EAGLE schematic design system. Pads is an interface to Mentor's PADS schematic design system. ECAD is an interface to ECAD schematic design system.
- **Gerber, SVG, Postscript:** Gerber is a PCB artwork file format. It contains all the information related to PCB layers required for fabrication. SVG is abbreviated as Scalable Vector Graphics; it is based on the XML language. It is used to capture the current cell window. Postscript is an Adobe printing language which is used to capture the current cell window.

2.3.6. Parasitic Extraction

Parasitic capacitance and resistance of the interconnect influences and affects the performance of VLSI circuits. With the decrease in transistor feature size and increase in circuit performance (higher speeds) interconnect parasitic effects are becoming more important. Hence, there is a need to extract the parasitics from the active devices, and the wire interconnects of an IC for synthesizing the design. Parasitics are extracted from the simulations of the physical design of an IC using analog/SPIICE simulators. Electric provides the designers to extract the parasitics from the layout, using **preferences** of Electric, under

Tools/parasitic section one has to check the boxes of **Extract R** and **Extract C** and then under **Tools/Spice/CDL** section one has to choose **Conservative RC** option for **Parasitics** in the same **preferences** of Electric.

2.4. Design Flow in Electric

Digital and Analog designs in Electric follow the design flow shown in figure 2.8.

2.4.1. Schematic level Design

In Electric, all transistor-level designs are created in the schematics design environment. It has all the digital, analog and mixed-signal components that are needed to design the transistor-level designs. Figure 9(b) shows the components required to build the inverter in transistor-level. It needs a p-channel transistor, an n-channel transistor, voltage source, ground, wire, and input and output ports to send input and to get output voltages. The PMOS is connected to V_{dd} because it passes strong 1 and NMOS passes strong 0, hence PMOS is best for pull-up network, and NMOS is best for pull-down network. After designing the transistor level diagram of an inverter the next step is to check for any circuit connection errors with DRC tool and then simulate the circuit for schematic verification. LTspice or other SPICE simulators can be used to check the design.

2.4.2. Physical level Design

Once the schematic design is ready, the next step is to translate the schematic design to device and wire placements on silicon [6]. This level is called physical level. In Electric the layout of a schematic diagram is drawn in the “mocmos” design environment. There are many technologies present in Electric as design environments. For a standard CMOS technology, the user can choose mocmos, mocmossub, etc. depending on the technology size. For an 180 nm design mocmos is a perfect choice. In Electric for laying out the inverter at the physical level, we need a P-channel transistor, N-channel transistor, P-well, N-well, N-active and p-active components. We also need a P-active arc, N-active arc, metal-1 arc

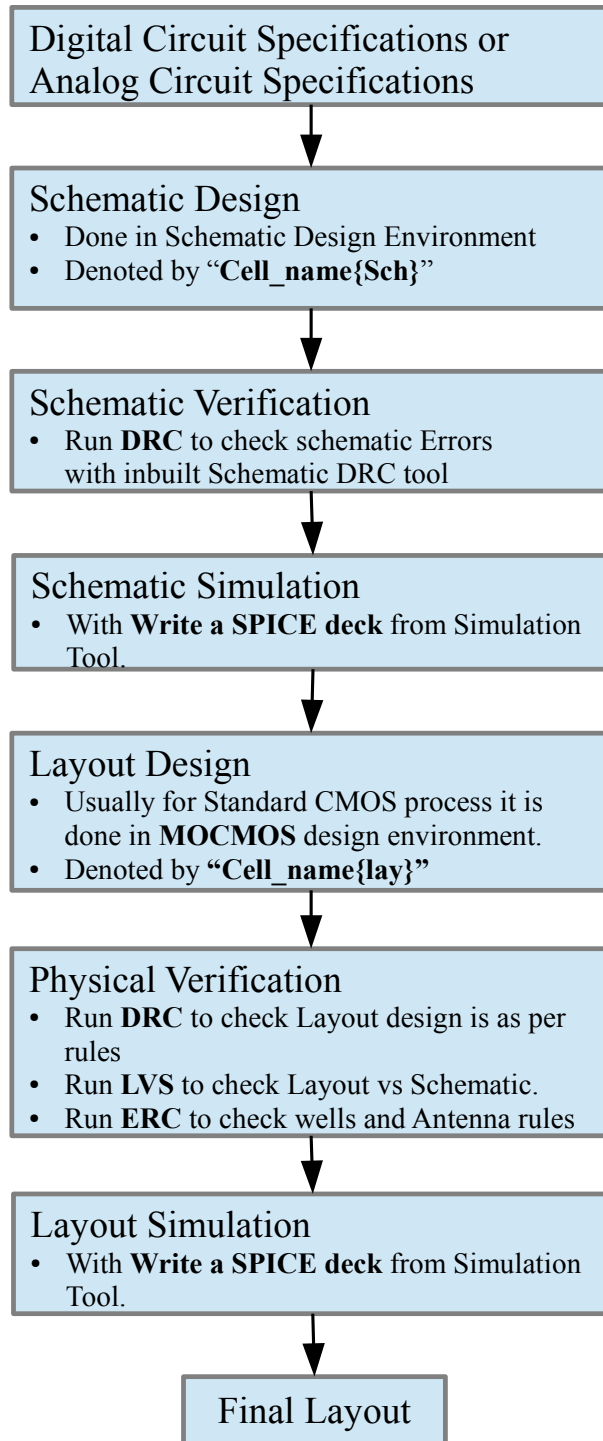
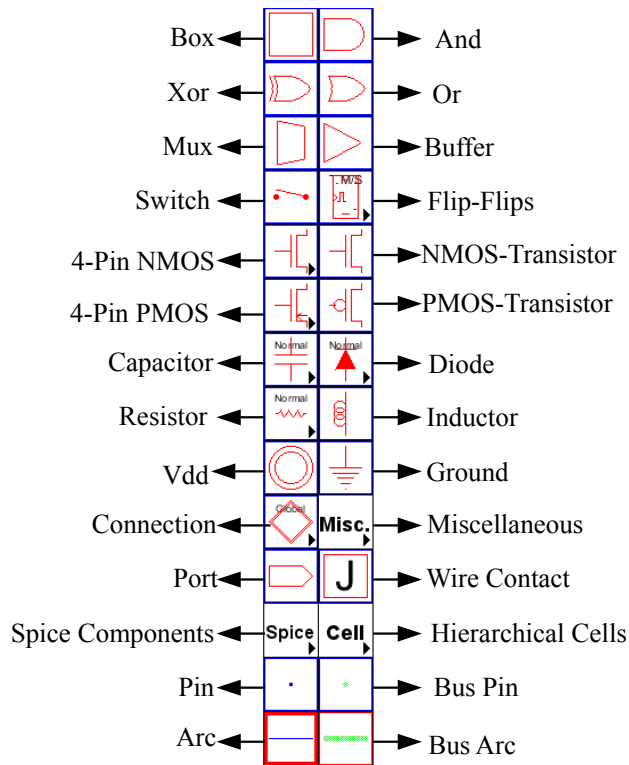
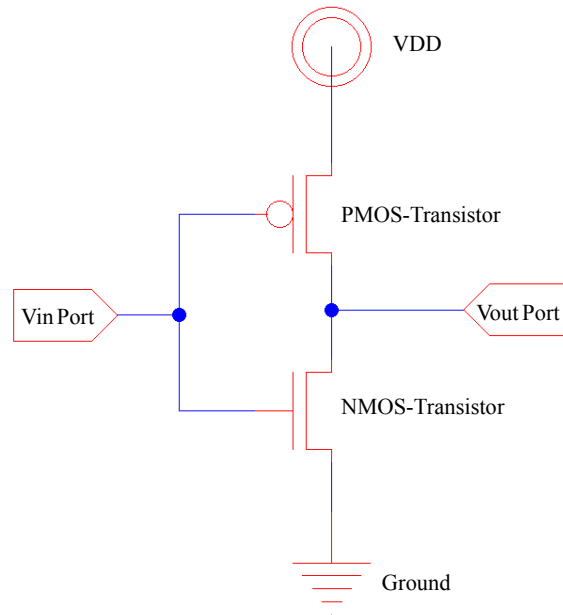


FIGURE 2.8. Electric Design Flow.

and poly arc. All these arcs are formed when components are connected. Figure 2.10 shows the components and actual layout design of an inverter using the components. After layout



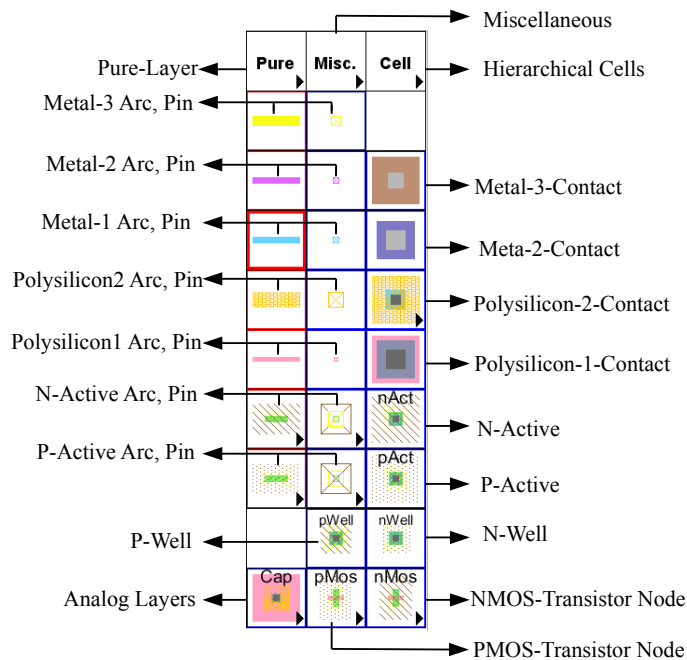
(a) Schematic design components.



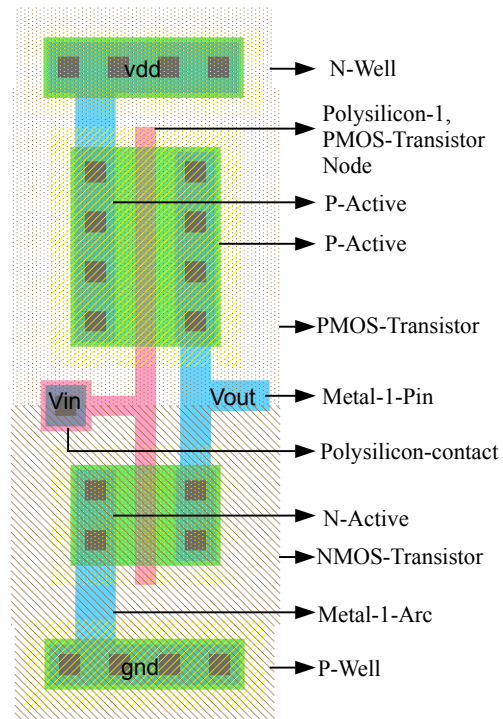
(b) Schematic design of an Inverter.

FIGURE 2.9. Schematic level components and design.

design of an inverter, next step is to check for any layout design errors using DRC. Design errors in layout design are harder to rectify than errors in schematic design. LVS (Layout vs. Schematic) is used in this design to check that the layout design is actual representing the schematic circuit, and then one can check for well and antenna rules if necessary. Layout simulation can also be done similar to schematic design simulation.



(a) Physical design layers and components.



(b) Layout design of an inverter.

FIGURE 2.10. Physical level components and design.

2.5. Scripting in Electric

Electric allows Python and Java programming languages as scripting languages to run on the software. Scripting helps to automate the design flow. Scripting is used by many leading EDA companies such as Mentor Graphics, Synopsys, Cadence, etc. to reduce the time and work needed to establish design flows. It also reduces human errors that may be caused when designing very large integrated circuits. Python is a widely used high-level programming language. It supports objects oriented concepts, multiple programming paradigms, and is also used for scientific computing. Electric uses Jython to run python scripts and Beam shell plugin to run Java on it. By using scripting languages in Electric, one can design a circuit in schematics and lay it out in the same technology. Some of the Python scripts are listed below. The first python script listed creates a layout cell in mocmos technology and names it as sample1. The classes and methods which are used to create the

cell are known from the Javadoc file of Electric. The second python script creates a two input inverter layout diagram with cell name sample2.

```
1 from com.sun.electric.database.hierarchy import Cell
2 from com.sun.electric.database.hierarchy import Library
3 from com.sun.electric.database.topology import NodeInst
4 from com.sun.electric.database.variable import EvalJython
5 from com.sun.electric.technology import Technology
6 from java.awt.geom import Point2D
7 newCell = Cell.makeInstance(Library.getCurrent(), "sample1{lay}")
8 tech = Technology.findTechnology("mocmos")
9 trP = tech.findNodeProto("P-Transistor")
10 tP = NodeInst.makeInstance(trP, Point2D.Double(10, 10), trP.getDefWidth(), trP
    .getDefHeight(), newCell)
11 EvalJython.displayCell(newCell)
```

```
1 from com.sun.electric.database.hierarchy import Cell
2 from com.sun.electric.database.hierarchy import Library
3 from com.sun.electric.database.hierarchy import Export
4 from com.sun.electric.database.prototype import PortCharacteristic
5 from com.sun.electric.database.topology import ArcInst
6 from com.sun.electric.database.topology import NodeInst
7 from com.sun.electric.database.topology import Geometric
8 from com.sun.electric.technology import Technology
9 from com.sun.electric.database import EditingPreferences
10 from java.awt.geom import Point2D
11 from com.sun.electric.tool import routing
12 from com.sun.electric.util.math import Orientation
13 # create the new cell
14 newCell = Cell.makeInstance(Library.getCurrent(), "sample2{lay}")
15 tech = Technology.findTechnology("mocmos")
16 # place a rotated transistor
```

```

17 trP = tech.findNodeProto("P-Transistor")
18 tP = NodeInst.makeInstance(trP, Point2D.Double(0, 20), 32, trP.getDefHeight(),
    newCell, Orientation.R, "pmos")
19 # place a metal-Active contact
20 coP = tech.findNodeProto("Metal-1-P-Active-Con")
21 maP = NodeInst.makeInstance(coP, Point2D.Double(5, 20), coP.getDefWidth(), 32,
    newCell)
22 # place a metal-Active contact
23 coP1 = tech.findNodeProto("Metal-1-P-Active-Con")
24 maP1 = NodeInst.makeInstance(coP1, Point2D.Double(-5, 20), coP1.getDefWidth(),
    32, newCell)
25 # wire the transistor to the contact
26 aP = tech.findArcProto("P-Active")
27 ArcInst.makeInstance(aP, tP.findPortInst("diff-bottom"), maP.findPortInst("
    metal-1-p-act"))
28 # wire the transistor to the contact
29 ArcInst.makeInstance(aP, tP.findPortInst("diff-top"), maP1.findPortInst("metal
    -1-p-act"))
30 # place a rotated transistor
31 trP1 = tech.findNodeProto("N-Transistor")
32 tP1 = NodeInst.makeInstance(trP1, Point2D.Double(0, -7), 22, trP1.getDefHeight
    (), newCell, Orientation.R, "nmos")
33 # place a metal-Active contact
34 coN = tech.findNodeProto("Metal-1-N-Active-Con")
35 maN = NodeInst.makeInstance(coN, Point2D.Double(5, -7), coN.getDefWidth(), 22,
    newCell)
36 # place a metal-Active contact
37 coN1 = tech.findNodeProto("Metal-1-N-Active-Con")
38 maN1 = NodeInst.makeInstance(coN1, Point2D.Double(-5, -7), coN1.getDefWidth(),
    22, newCell)
39 # wire the transistor to the contact

```



```

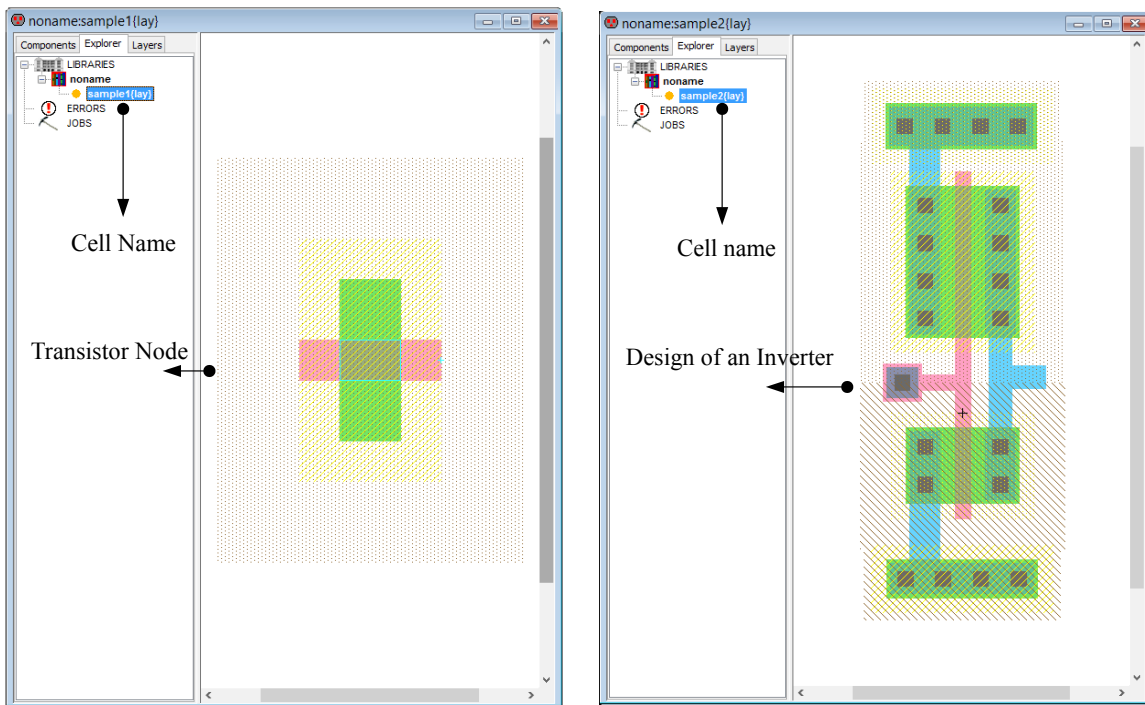
40 aP1 = tech.findArcProto("N-Active")
41 ArcInst.makeInstance(aP1, tP1.findPortInst("diff-bottom"), maN.findPortInst("
    metal-1-n-act"))
42 # wire the transistor to the contact
43 ArcInst.makeInstance(aP1, tP1.findPortInst("diff-top"), maN1.findPortInst("
    metal-1-n-act"))
44 #poly to poly connect
45 poly2=tech.findArcProto("Polysilicon-1")
46 p2p=ArcInst.makeInstance(poly2, tP.findPortInst("poly-left"), tP1.findPortInst
    ("poly-right"))
47 #metal to metal
48 metal1=tech.findArcProto("Metal-1")
49 ArcInst.makeInstance(metal1, maP.findPortInst("metal-1-p-act"), maN.
    findPortInst("metal-1-n-act"))
50 #N-well on top
51 nwell= tech.findNodeProto("Metal-1-N-Well-Con")
52 nwell1=NodeInst.makeInstance(nwell, Point2D.Double(-5, 38), 32, 18, newCell)
53 center=ArcInst.makeInstance(metal1, nwell1.findPortInst("metal-1-substrate"),
    maP1.findPortInst("metal-1-p-act") )
54 ArcInst.getTailPortInst(center)
55 Export.newInstance(newCell, nwell1.findPortInst("metal-1-substrate"), "vdd",
    PortCharacteristic.IN)
56 pwell= tech.findNodeProto("Metal-1-P-Well-Con")
57 pwell1=NodeInst.makeInstance(pwell, Point2D.Double(-5, -22), 32, pwell.
    getDefHeight(), newCell)
58 center1=ArcInst.makeInstance(metal1, pwell1.findPortInst("metal-1-well"), maN1.
    findPortInst("metal-1-n-act") )
59 Export.newInstance(newCell, pwell1.findPortInst("metal-1-well"), "gnd",
    PortCharacteristic.IN)
60 #input contact
61 conpoly = tech.findNodeProto("Metal-1-Polysilicon-1-Con")

```

```

62 conpoly1 = NodeInst.makeInstance(conpoly, Point2D.Double(-8, 4), conpoly.
    getDefWidth(), conpoly.getDefHeight(), newCell)
63 erc=ArcInst.makeInstance(poly2,tP.findPortInst("poly-left"),conpoly1.
    findPortInst("metal-1-polysilicon-1"))
64 p=ArcInst.getArcId(erc)
65 print p
66 #output contact
67 conmet = tech.findNodeProto("Metal-1-Pin")
68 conmet1 = NodeInst.makeInstance(conmet, Point2D.Double(10, 5), conmet.
    getDefWidth(), conmet.getDefHeight(), newCell)

```



(a) Layout design of transistor node using Python script. (b) Layout design of an Inverter using Python script.

FIGURE 2.11. Outputs for scripts running in Electric

Package	Class	Method	Description
com.sun.Electric. database.hierarchy	Cell	makeInstance()	This method creates a cell
com.sun.Electric. technology	Technology	findTechnology()	This method finds the re- quired technology
com.sun.Electric. technology	Technology	findNodeProto()	This method returns the primitiveNode name in that technology
com.sun.Electric. technology	Technology	findArcProto()	This method returns the ArcProto name in that tech- nology
com.sun.Electric. database.topology	NodeInst	makeInstance()	Creates a NodeInst and do extra things necessary for it.
com.sun.Electric. database.topology	ArcInst	makeInstance()	Creates ArcInst with appro- priate defaults, connecting two PortInsts

TABLE 2.4. Important Methods for Designing in mocmos technology.

2.6. Electric Advantages

- Integrity: It is very rare for an open source EDA tool where schematics and layout design with simulation are done in one tool. The Electric VLSI design system is a single user interface where schematics and IC layout designs are done. It has LVS (Layout vs. Schematic) check to check and compare both designs.
- No node extraction: Node extraction is one of the steps in the design flow for designs to see connectivity of layout. In Electric there is no need to separately do this step as it is instantly available with the connectivity part of it. Connectivity is the crucial thing in physical design level. It must be verified during or right after the design,

but most conventional design systems wait for a finished layout. This causes many errors in the physical layout. The process of converting the design to connected circuitry from pure geometry is called node extraction.

- No geometry errors: Layers have different minimum geometry rules. In Electric components which have complex geometries are set as one single component and can be edited for change of size. Transistor is one such example.
- Simpler design process: In physical design stage of design, designers usually iterate between DRC (Design rule checking) and Layout vs Schematic (LVS). The problem is that LVS needs to know the circuit connectivity, which is obtained by the node extraction process, which can only run after DRC. Hence the layout must be DRC clean before running LVS. When LVS has problems, one has to edit the layout and make it DRC clean again, which takes a lot of time. In Electric, the first step is to know the layout vs schematic errors and then one can easily edit the layout without fear of losing the LVS match.
- More powerful editing: Because Electric shows the network information even in Integrated circuit layout, browsing the circuit has become more powerful and gives a lot of information about it. Since Electric is connectivity based tool, the tools in Electric make the circuit always connected, even when the circuit is modified on different hierarchy levels.

CHAPTER 3

DIGITAL INTEGRATED CIRCUIT DESIGN USING ELECTRIC

In this chapter, digital circuits are explored with the help of the Electric EDA tool. A combinational circuit, a sequential circuit, a memory design and an arithmetic logic unit circuit are chosen for four digital designs in this chapter. All the standard digital circuits such as Inverter, AND gate, NAND gate, etc. that a student needs to learn are covered in this chapter, showing the schematic level design, the physical level design and also simulations for that design. All designs are drawn from standard textbooks and existing research literature. The physical level designs are all drawn, following MOSIS design rules for TSMC 180nm technology. The model files for transistors are taken from the official MOSIS site.

3.1. ALU

The ALU (Arithmetic and Logic Unit) is a main and crucial part in a CPU (Central Processing Unit). The ALU is used in almost every computing application for all logical and mathematical operations. It is a multi-functional circuit which can perform many operations such as AND, NOR, addition, subtraction, etc. without depending on control units. Figure 3.1 shows an 1-bit ALU, which is formed with AND gate, OR gate, full adder, and three 2to1 multiplexers. It performs AND, OR, addition and subtraction operations. Here the AND gate and OR gates are used for directly performing AND and OR operations and the full-adder performs the addition and subtraction operations. A multiplexer is used to control the operations. The other two multiplexers are used for sending the right operation result to the output. Hence, the 1-bit ALU is formed with six gate level components[27].

3.1.1. Gate level Components

3.1.1.1. Inverter

The inverter is a most important and central block of all digital designs. The working principle of the inverter is that when the input is connected to ground, the output is pulled

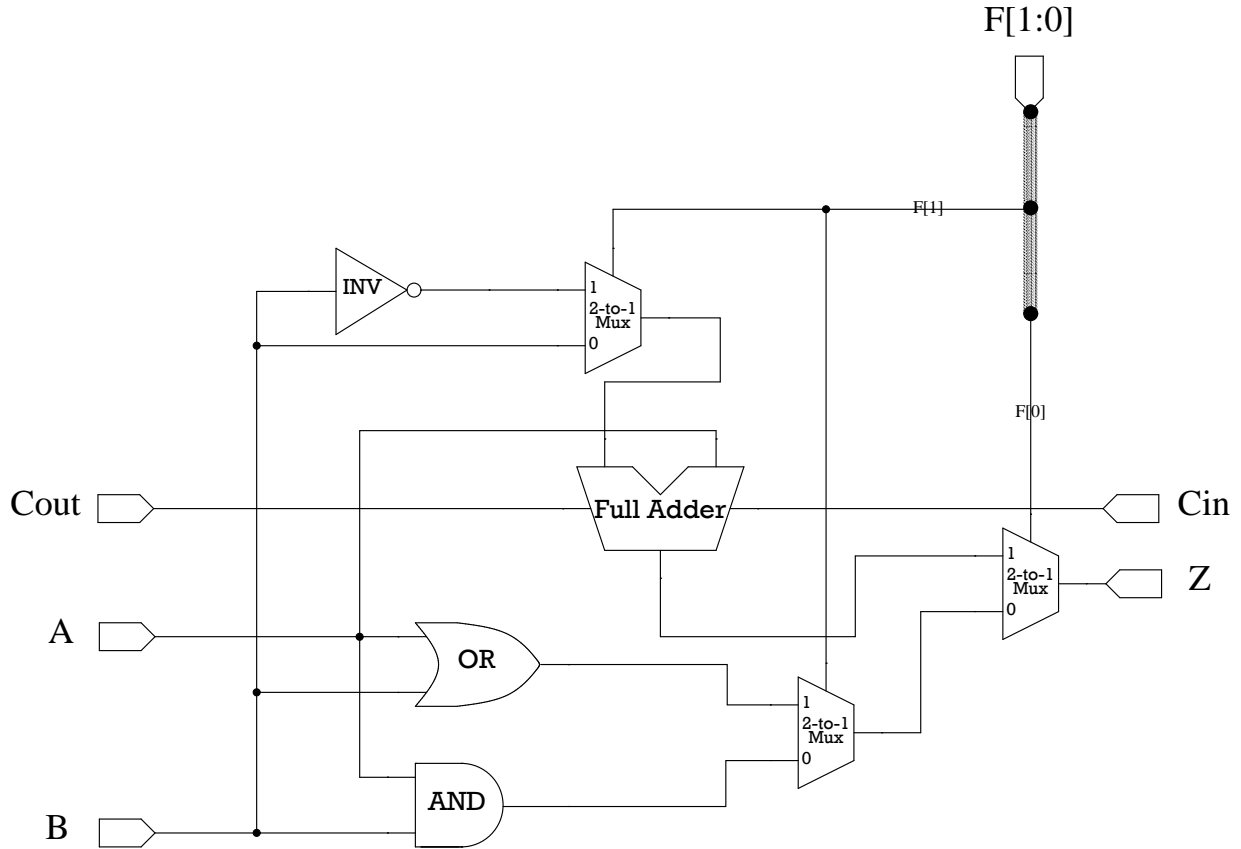


FIGURE 3.1. 1-bit ALU schematic diagram.

to V_{DD} through the PMOS. When the input is connected to the source, the output is pulled down to ground through the NMOS. The inverter has one p-channel transistor and one n-channel transistor which are connected to source and ground, respectively [3]. Figure 3.2 shows the transistor level diagram of an inverter. It has a PMOS and NMOS connected in series, and also a voltage source V_{DD} and ground are connected to these transistors. Figure 3.3 shows the physical diagram of an inverter, the PMOS and NMOS transistors are drawn as devices. The input port V_{in} formed with Polysilicon-1 contact and Metal-1 pin is used for the V_{out} port. Only Metal-1 arc and polysilicon arc is used for connecting the devices. The layout area of the implemented Inverter is $58.3\mu\text{m} \times 12.2.1\mu\text{m}$. Figure 3.4 shows the simulation result for an inverter. When V_{in} is HIGH the output at V_{out} is LOW. Similarly, when V_{in} is LOW the output at V_{out} is HIGH.

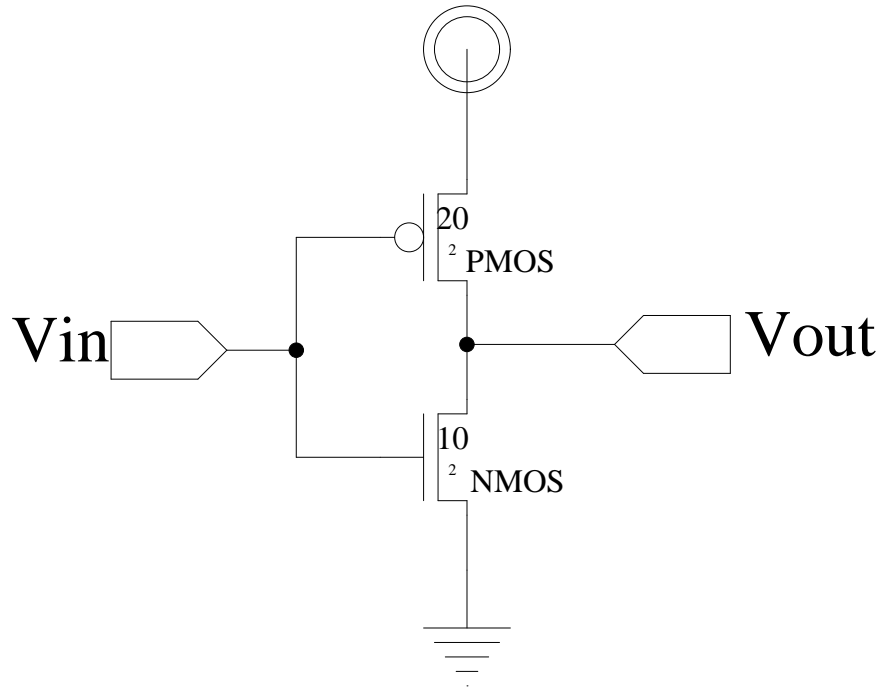


FIGURE 3.2. Inverter schematic diagram.

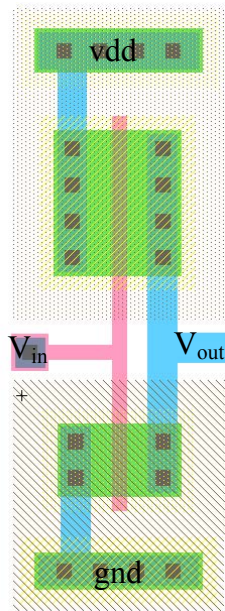


FIGURE 3.3. Layout Diagram of an Inverter.

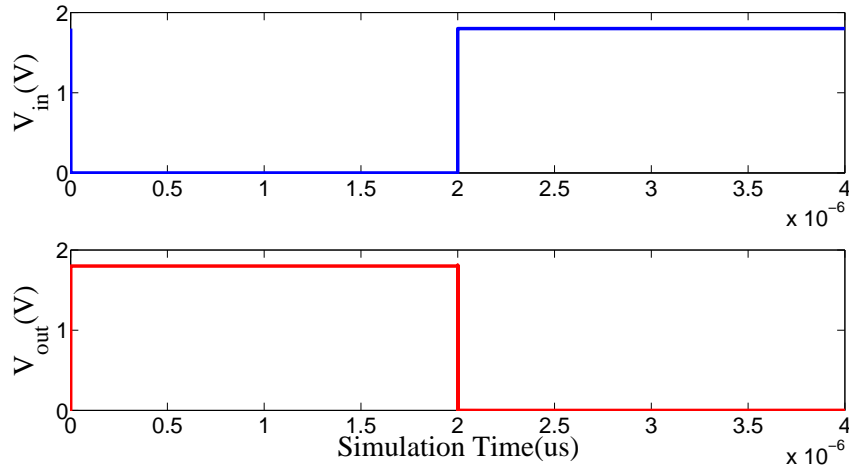


FIGURE 3.4. Simulation results for Inverter.

3.1.1.2. OR gate

The OR gate is one of the basic logic circuits in the combinational logic gates family. OR gate consists of three series PMOS transistors and three parallel NMOS transistors. It is formed with NOR gate and an inverter connected to V_{DD} and ground and has two inputs A and B, and output AORB. When both input signals A and B are LOW, the output AORB is also LOW. For the other cases the output is always HIGH. Figure 3.5 shows the schematic diagram of an OR gate. The sizings of the transistors are done as per the technology model file. The fan-in count of the OR gate is 2, and the fan-out count is 1. Fan-in of a logic gate is the number of gates present in the input and fan-out is a total number of gates that are driven by gate output. Figure 3.6 shows the layout diagram of an OR gate. The layout area of the implemented OR gate is $79.32\mu\text{m} \times 75.1\mu\text{m}$. Here for the input signals A and B polysilicon-1 contact is used and for the output AORB, the metal-1 pin is used. All the connections are drawn using polysilicon arc and metal-1 arc. Figure 3.7 shows the simulation results for the OR gate. When V_A and V_B are LOW the output voltage V_{AORB} is LOW. For the rest of the cases the output voltage V_{AORB} is always HIGH.

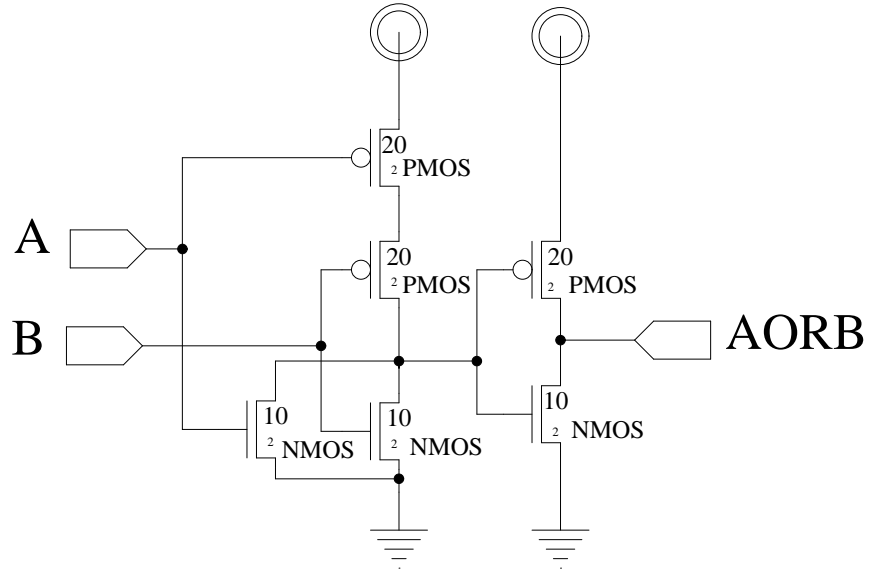


FIGURE 3.5. Schematic diagram of an OR gate.

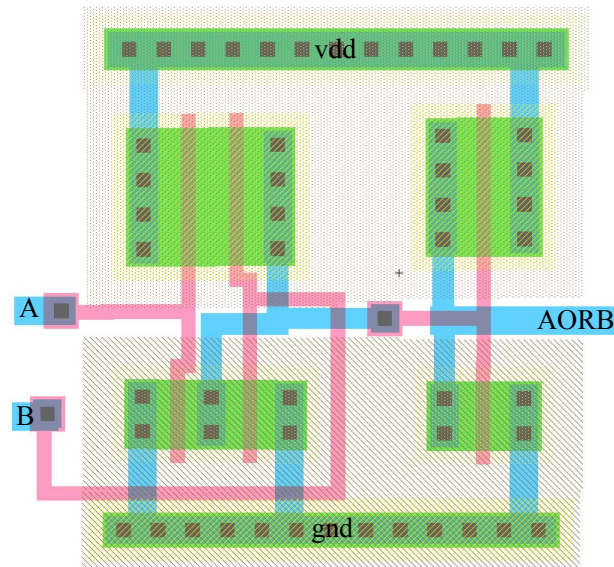


FIGURE 3.6. Layout diagram of an OR gate.

3.1.1.3. AND Gate

The AND gate is formed with a NAND gate and an inverter. It consists of three PMOS transistors connected in parallel and three NMOS transistors connected in series. Figure 3.8 shows the schematic diagram of an AND gate. It has two inputs A and B, and output $A \text{ AND } B$. When A and B are HIGH, the output $A \text{ AND } B$ is HIGH. For the rest of the

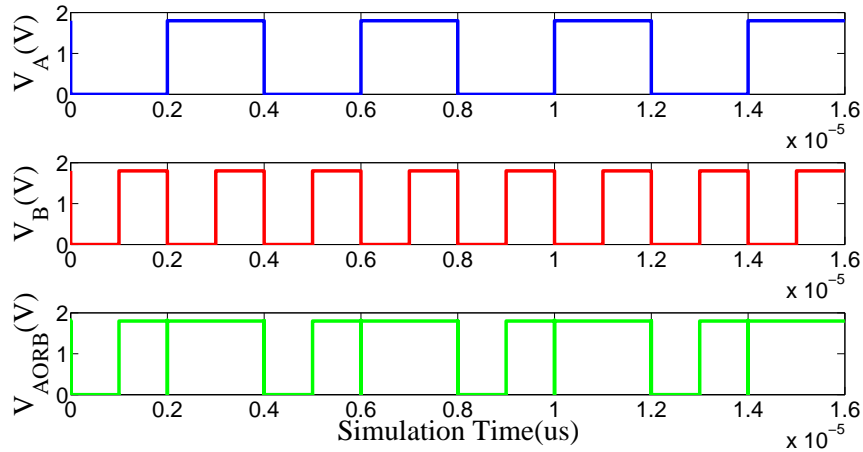


FIGURE 3.7. Simulation results of an OR gate.

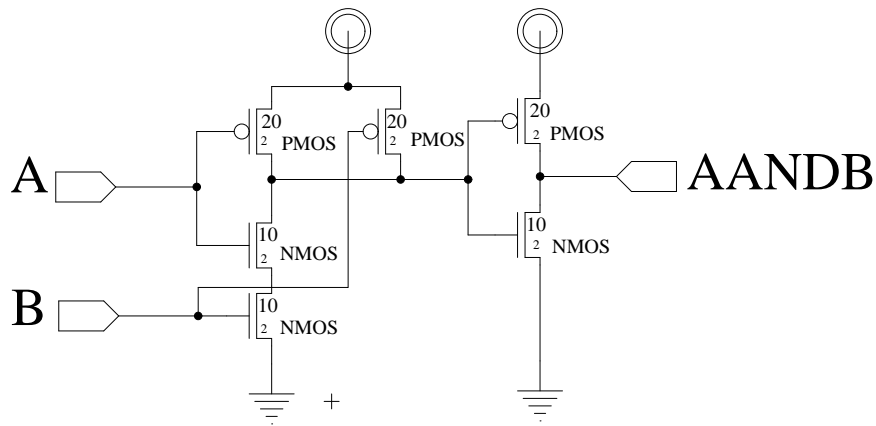


FIGURE 3.8. Schematic diagram of an AND gate.

cases the output is LOW. Figure 3.9 shows the layout diagram of an AND gate. Polysilicon-1 contacts are used for the A and B inputs, the metal-1 pin is used for the AANDB output. Figure 3.10 shows the simulation result of an AND gate. The layout area of the implemented AND gate is $80.5\mu\text{m} \times 70.4\mu\text{m}$. The result shows the same when A and B input are HIGH, the output AANDB is HIGH and rest of all cases it is LOW.

3.1.1.4. MUX

The multiplexer is a digital switch that has multiple inputs and a single output. It chooses one of many inputs and sends a single output through it with the help of control

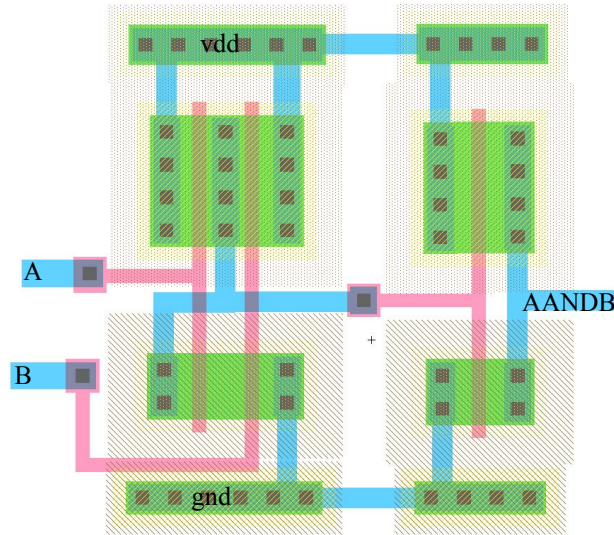


FIGURE 3.9. Layout diagram of an AND gate.

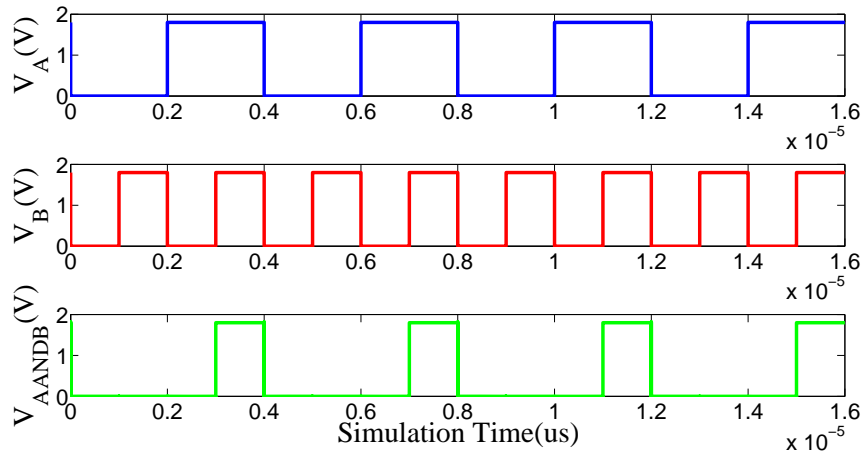


FIGURE 3.10. Simulation results for AND gate.

inputs. Here a 2 to 1 multiplexer is used to build the 8-bit ALU. Transmission gates are used to build the multiplexer. A transmission gate is a complementary switch, which is formed by parallel connection of PMOS and NMOS transistors. Figure 3.11 displays the schematic diagram of a multiplexer. It is built with two transmission gates and one inverter. A total of 6 transistors is used to create the multiplexer. Figure 3.12 shows the layout diagram of the multiplexer. Metal-2 contacts are used for inputs A and B, polysilicon-1 contact and metal-1 pin are used for the S and Z respectively. The layout area of the implemented MUX

is $130.5\mu\text{m}\times 94.5\mu\text{m}$ [10].

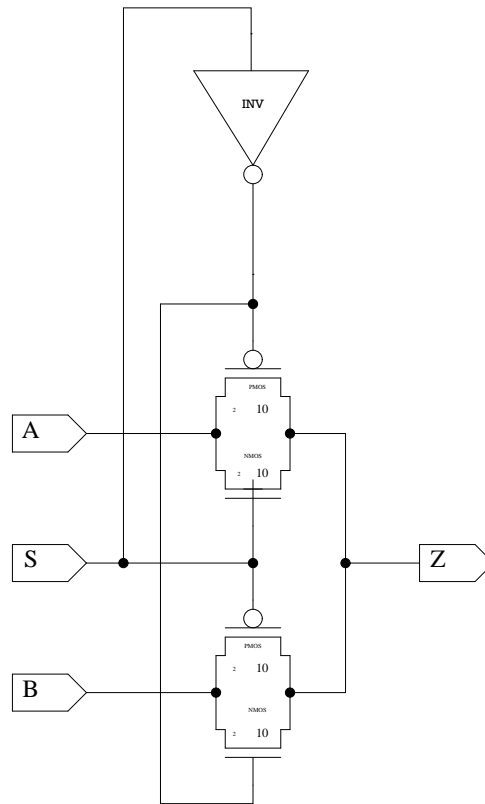


FIGURE 3.11. Schematic diagram of a MUX.

3.1.1.5. Full Adder

Adders play a very crucial role in VLSI systems. Microprocessors, digital signal processing architectures, parity checkers, etc. use adders in their applications. Here a full 28 transistor conventional adder is implemented. In static CMOS, the NMOS passes 0's, and PMOS passes 1's hence the levels will never be degraded. The advantages of CMOS full adders is that the layout is straight forward since the transistors are complementary, and it has high noise margins and stability at low voltages due to a complementary pair of transistors [1]. Other than the A and B inputs it also has a C_{in} input which is the carry of the sum from the previous operation. C_{out} and sum are the outputs of the full adder. Figure 3.13 shows the schematic diagram of a full adder. Figure 3.14 shows the layout diagram of a full adder. Here polysilicon-1 is used for A and B inputs, and the metal-2 pin is used for

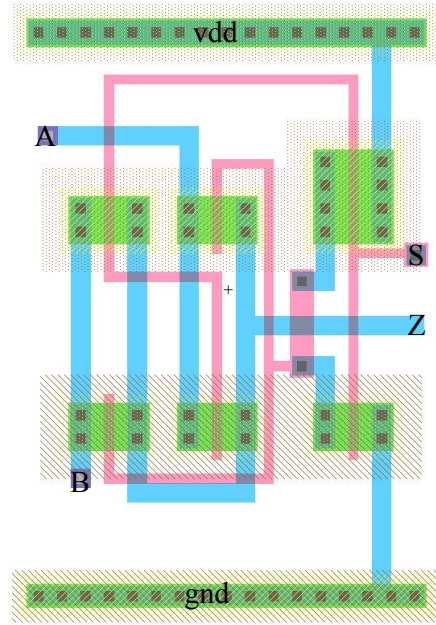


FIGURE 3.12. Layout diagram of a MUX.

C_{in} input. The outputs are formed with metal-1 pins. For connections, poly arc, metal-1 arc, and metal-2 are used in drawing the full adder layout circuit. The layout area of the implemented adder is $306.9\mu\text{m} \times 406.2\mu\text{m}$. Figure 3.15 shows the simulation results for a full adder. When A is 1, B is 0, and C_{in} is 0 the sum is 1 and C_{out} is 0. Similarly, when A is 1, B is 0 and C_{in} is 1 then the sum is 0 and C_{out} is 1.

3.1.2. Implementation of AN 8-bit ALU

In electric, there is an arc called bus that can be used to connect components similar to wire. Its advantage is that instead of creating multiple input wires a single bus is used and can export to multiple inputs. This benefit of a bus is useful in designing schematic circuits which have multiple inputs and outputs. The ALU has 8-bits A and B inputs and 8-bits of output Z, carry in and carry out and it also has two extra input bits to choose which function that ALU should perform. Table 3.1 shows the functions which are performed by the 8-bit ALU, which can be selected by two bits of F inputs. Table 3.2 shows the binary output values for a given set of input values. In the simulation of the 8-bit ALU the input A and B binary values are fixed and then with changing the function bits of ALU the operations AND,

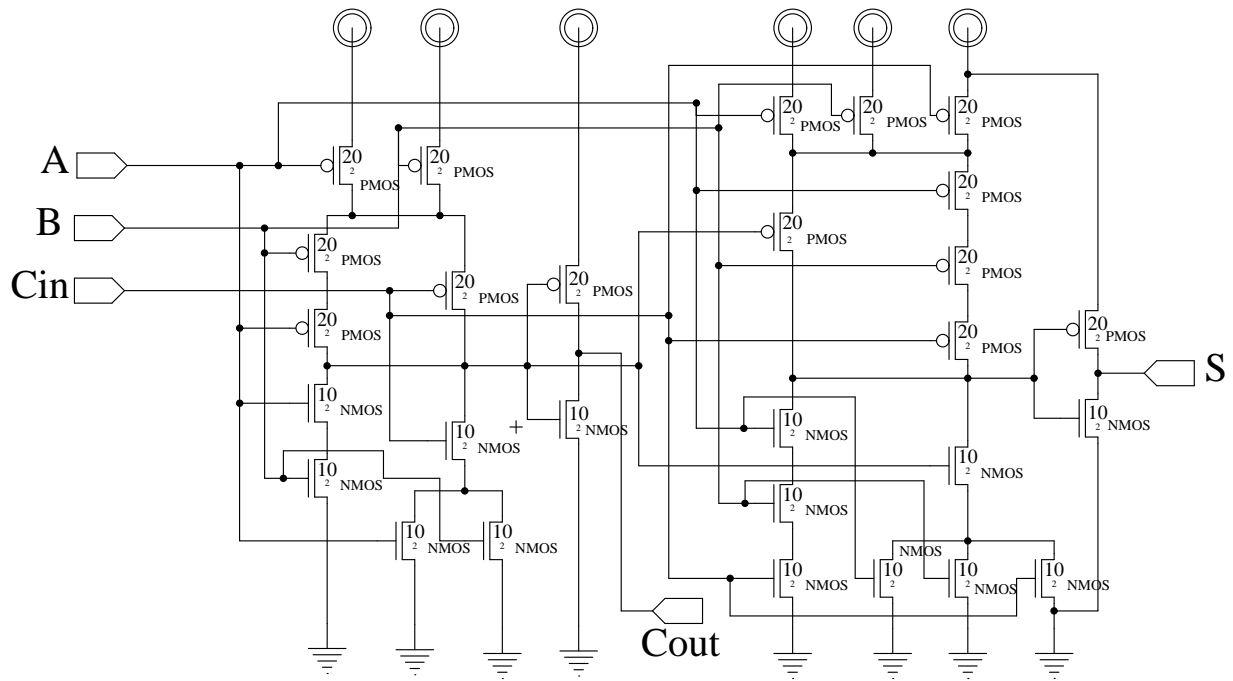


FIGURE 3.13. Schematic Diagram of a Full Adder.

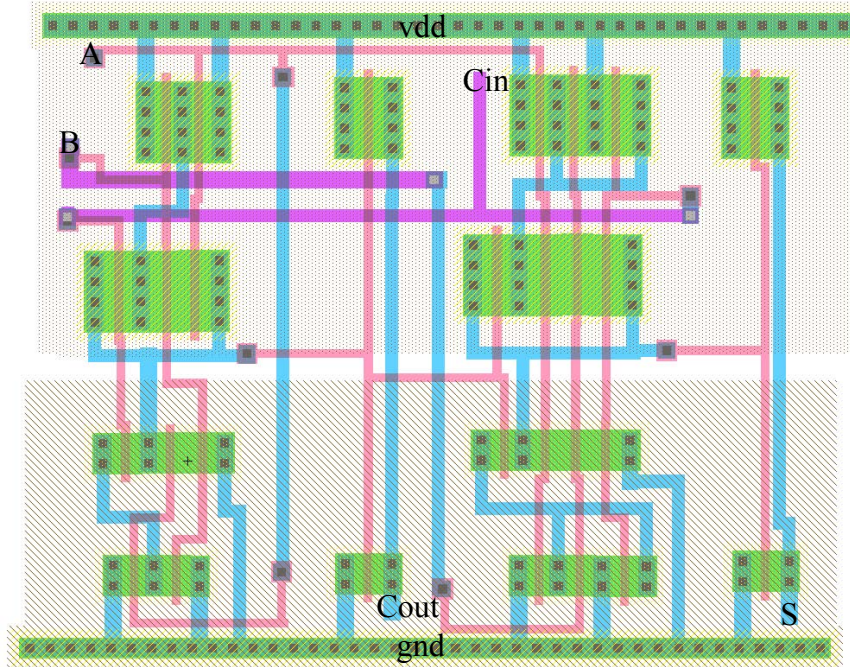


FIGURE 3.14. Layout Diagram of a Full adder.

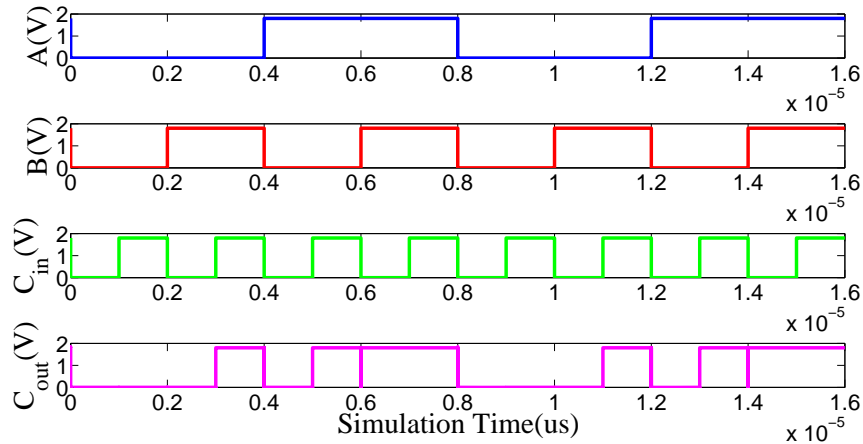


FIGURE 3.15. Simulation results for a Full adder

addition, subtraction, and OR are performed. Figure 3.16 displays the simulation results of the 8-bit ALU. The outputs of all Z0 to Z7 are shown in the simulation results. AND operation is performed by 8-bit ALU till time period 1, addition operation is performed from time period 1 to 2, OR operation is performed from the time period 2 to 3 and subtraction operation is performed by 8-bit ALU from time period 3 to 4. Figure 3.17 shows the layout diagram of an 8-bit ALU. The placement of all the layout blocks of gate level components results in minimum area. For connections, the metal-1,2,3 arc are used and for inputs and outputs polysilicon-1, metal-1,2,3 contacts are used. There were no errors in DRC (Design Rule Checker) check and it also satisfied the LVS (layout vs. schematic) check. The layout area of the implemented 8-bit ALU is $582.7\mu\text{m} \times 2357.9\mu\text{m}$.

3.2. 2-Bit Multiplier

Multiplication is necessary for the arithmetic operations that are performed by the processor. In this section, a 2-bit multiplier circuit is used to perform the operation. This 2-bit multiplier circuit consists of two half-adder circuits and 4 AND gate circuits which is a combinational circuit [16] where the output depends on the inputs and not past output values. The multiplication is done by the simple sum of the partial products technique and it is illustrated in figure 3.20. The product of multiplicand and multiplier bits is done using

F ₁	F ₀	Function
0	0	AND
0	1	ADD
1	0	OR
1	1	SUB

TABLE 3.1. Functions selected by 2-bit F inputs

Inputs	Value
A	01010001
B	10101100

Outputs	Value
AANDB	00000000
AORB	11111101
A+B	11111101
A-B	10100101

TABLE 3.2. Input and output values for 8-bit ALU

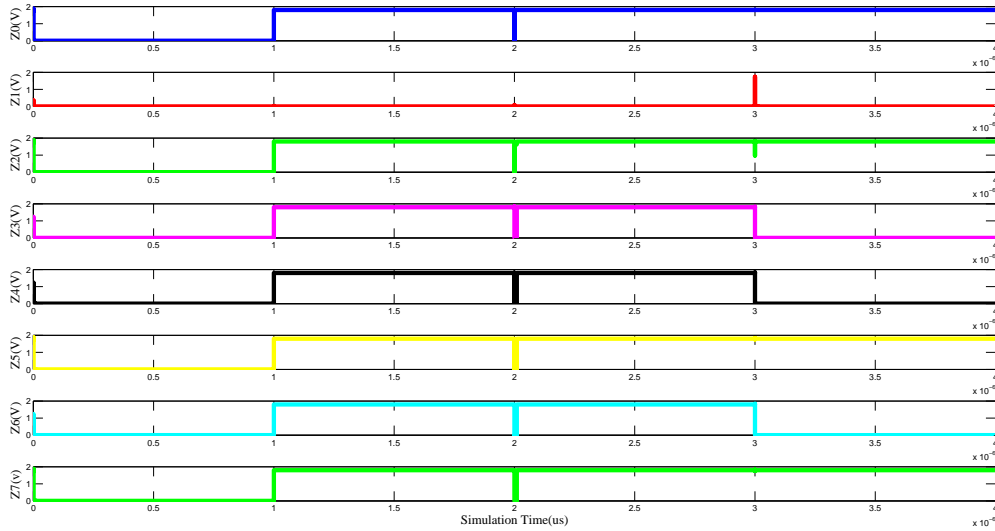


FIGURE 3.16. Simulation results for 8-bit ALU.

AND gates to get the partial products then the partial products are added using half-adder circuits to get 4 bits output that is the final product of 2-bit multiplier. if there is a J bits multiplier and a K bits multiplicand we need $J \times K$ AND gates and $(J-1) \times K$ half adders to get the product for $J+K$ bits.

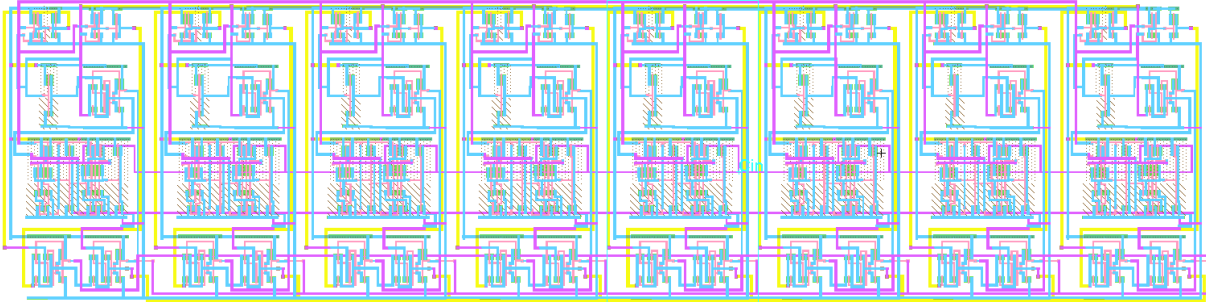


FIGURE 3.17. Layout Diagram of a Full adder.

3.2.1. Logic Level Components

3.2.1.1. Half-Adder

A typical adder is a digital combinational circuit which is used to add two numbers. It has two outputs port for sum bit (s) and carry bit (c). Many adders can be realized for binary numbers, binary coded decimal (BCD), etc. Adder circuits can be used in many applications in digital electronics. For example, they are used for addressing decoding, table index calculation, etc. There are two types of adder circuits: Half-adder and Full-adder. In this section a half-adder circuit is implemented. A half adder circuit adds two numbers and produces a sum bit(s) and carry bit (c) as outputs. The gate level components of half adder circuit are XOR and NAND gates. With XOR of A and B, the sum bit is produced and with A NAND B the carry bit is produced. Half adder circuit adds only two number and produces sum if there is any carry as input to the half adder, it will be neglected. Hence, it is called half adder. Figure 3.18 displays the schematic circuit of a half adder. It is formed with an XOR gate and an AND gate. Figure 3.19 shows the layout diagram of a half adder. Metal-2 contacts are used for input signal A and B, metal-pin and metal-3 contact is used for sum bit and carry bit respectively. All the connections are drawn using poly, metal-1,2 arcs. The layout area of the implemented Half-adder is $177.7\mu\text{m} \times 190.9\mu\text{m}$.

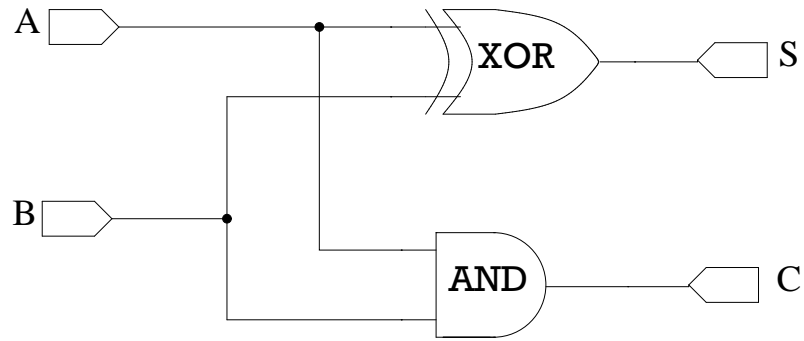


FIGURE 3.18. Schematic diagram of a half-adder.

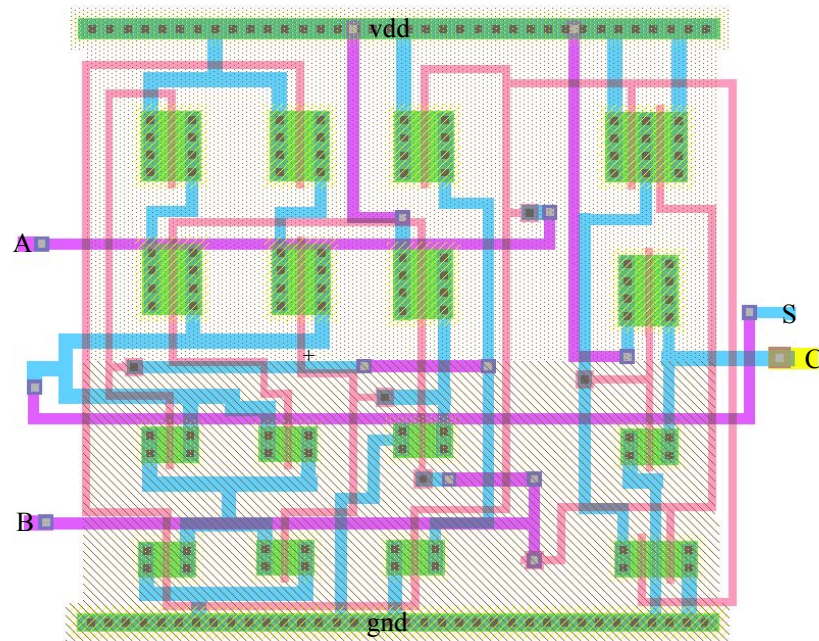


FIGURE 3.19. Layout diagram of a half-adder.

3.2.2. Implementation of a 2-bit Multiplier

Figure 3.21 shows the schematic diagram of a 2-bit multiplier. Gate level components are two half adders and four AND gates. It has four input bits A_0, A_1, B_0, B_1 and it has four outputs bits C_0, C_1, C_2, C_3 . This two-bit multiplier circuit multiplies two binary digits of one number to two binary digits of another number and gives four bits output. A normal multiplication process has a multiplicand and multiplier. The 2-bit multiplier works

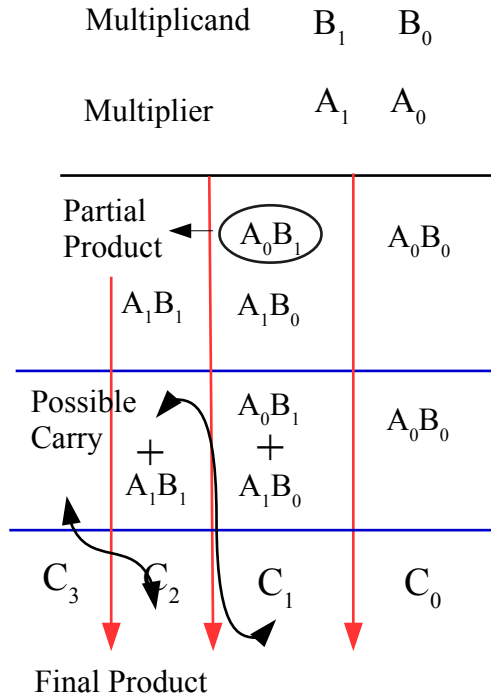


FIGURE 3.20. 2-bit multiplication process.

on the principle of the sum of partial products: the AND gate in the circuit multiplies both multiplicand bit and multiplier bit to give a partial product. All the partial products from the AND circuit output are added by the half adder circuit to get the final result. Figure 3.20 shows how the multiplication process is done using the schematic circuit. Here B_1 and B_0 are multiplicand bits and A_1 and A_0 are multiplier bits. A_0B_1 is a partial product, and it is added to another partial product A_1B_0 by a half adder and the result is obtained in C_1 . Figures 3.23 and 3.24 show the simulation results for the 2-bit multiplier. When A_1 is 0, A_0 is 1, B_1 is 0 and B_0 is 1 then the output C_0 is 1 and rest C_1 , C_2 , C_3 are zero. Similarly, when A_1 is 1, A_0 is 0, B_1 is 1 and B_0 is 0 then the output C_2 is 1 and rest C_1 , C_0 , C_3 are zero. Figure 3.22 shows the layout diagram of the 2-bit multiplier. For inputs and outputs, polysilicon-1, metal-1, metal-2 and also metal-3 contact are used and for connections poly arc, metal-1,2,3 arc are used. The layout area of the implemented 2-bit multiplier is $189.9\mu\text{m} \times 699.0\mu\text{m}$.

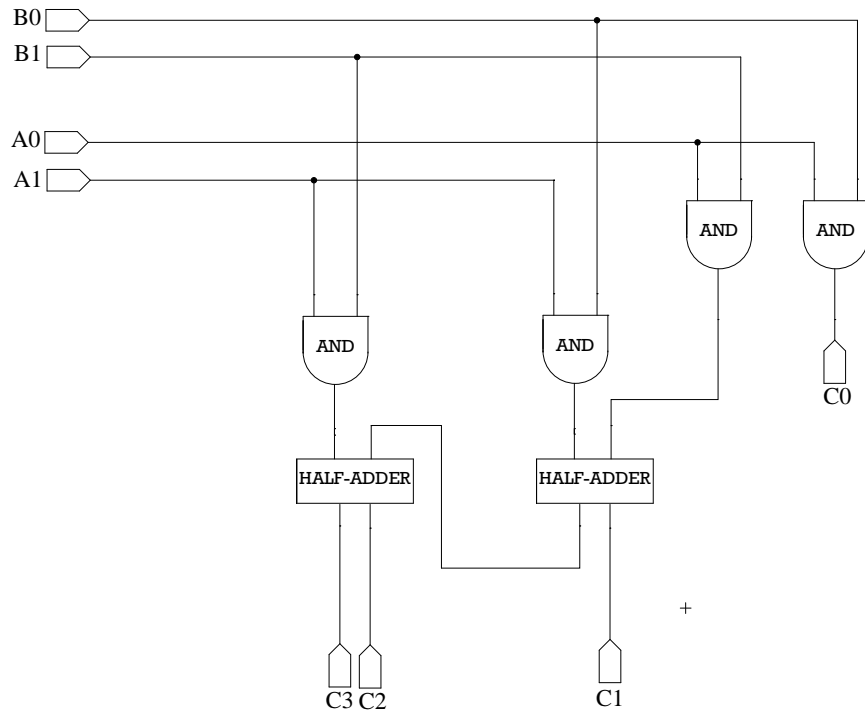


FIGURE 3.21. Schematic diagram of a 2-bit multiplier.

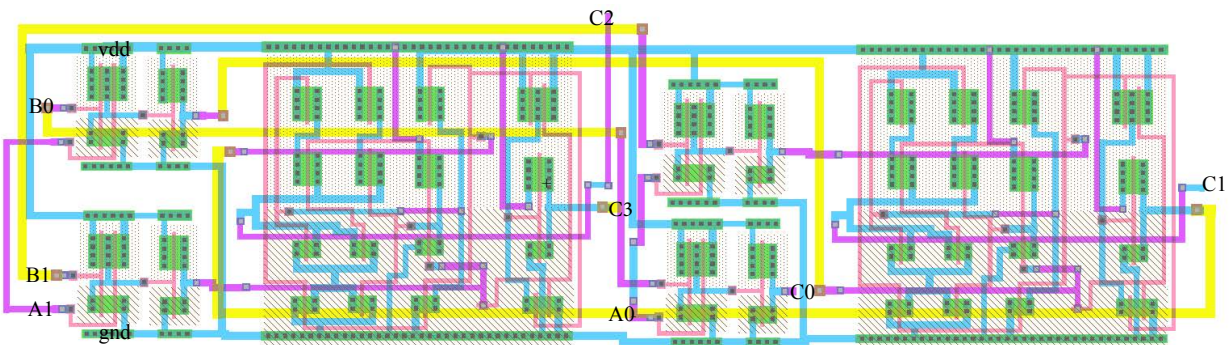


FIGURE 3.22. Layout diagram of a 2-bit multiplier.

3.3. Frequency Divider

A sequential logic circuit's output variable is not solely dependent on the input variable like combinational circuit but also it depends on the previous input variable's history [30]. For a sequential logic circuit, flip flops are the basic building blocks. In this design, a frequency divider is implemented using flip flops. The frequency divider (also called a clock divider) is a circuit that can reduce the frequency of an input signal passing through

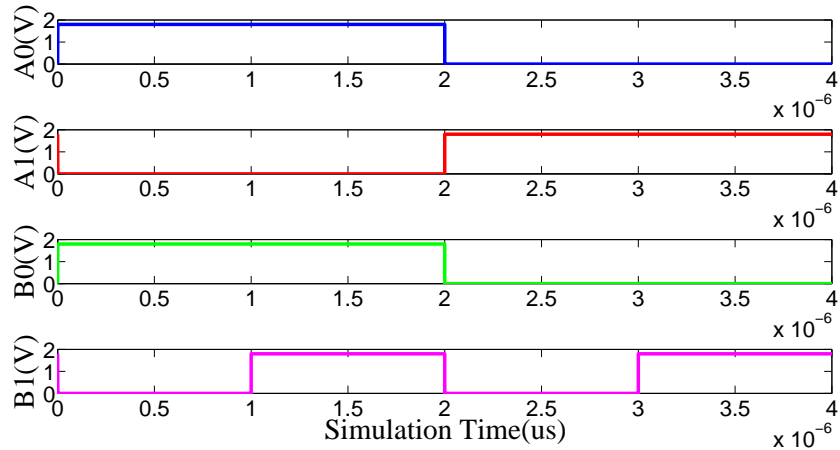


FIGURE 3.23. Input signals for a 2-bit multiplier.

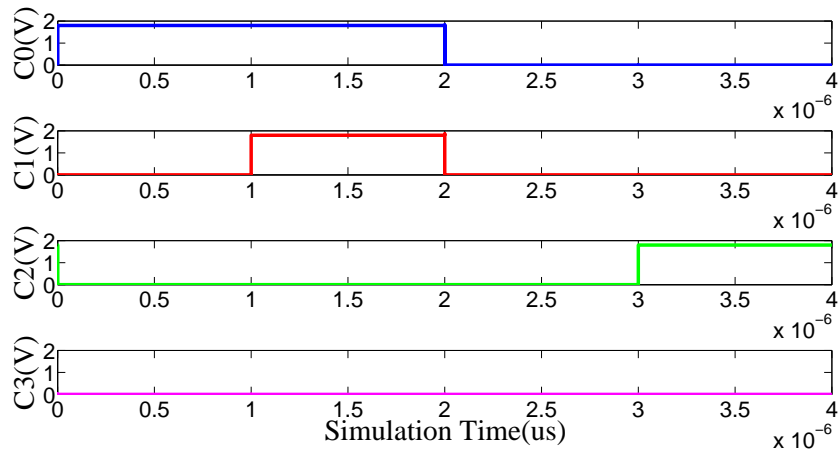


FIGURE 3.24. Output signals for a 2-bit multiplier.

it. There are various topologies and implementations for frequency dividers. Among all the divider solutions, the digital frequency divider is preferred because it gives good trade-offs in the areas of cost, power consumption, and physical dimensions [5]. The typical digital frequency divider is made with DFF (D flip-flops) or JK flip-flops. Here JK flip-flops are used to make a digital frequency divider. The JK flip-flops functions as counters which perform power-of-2 integer divisions [19].

3.3.1. Logic level Components

3.3.1.1. JK Flip-Flop

Master Slave JK Flip-flop is used for the frequency divider. At logic level, it consists of two three-input NAND gates, six two-input NAND gates, and one inverter 3.25. It is formed by a cascade connection of two S-R Flip-flops with feedback from the output of second S-R FF to the input of first. The slave will respond to the negative value of the clock signal since the inverter present is in clock line. Hence, when the clock is HIGH the master part of JK flip is active, and Slave part is inactive, similarly when the clock is LOW the master part is inactive, and slave is active. When $J=k=0$ the output will remain unchanged. This is because if the Clock is zero the slave will be active and master will be inactive, so there are no inputs from master to slave hence there is output from the slave. When $J=0$ and $K=1$ the output is $Q=0$ and $Q_{\text{Bar}}=1$, if the clock= one the Master is active, and slave is inactive. Hence, the outputs of the master are $Q1=0$ and $Q1_{\text{Bar}}=1$ so $S=0$ and $R=1$. If the clock is zero the Master is inactive, and slave is active. Therefore, outputs will be $Q=0$ and $Q_{\text{Bar}}=1$. Again when the clock is one the master is active, and slave is inactive, even though the output of slave is fed to master the output of master's remains same, i.e., $Q1=0$ and $Q1_{\text{Bar}}=1$. Thus, the outputs are stable from Master and Slave. When $J=1$ and $K=0$ the output is $Q=1$ and $Q=0$. If the clock is one the Master is active, and slave is inactive. Therefore, the outputs of the master are $Q1=1$ and $Q1_{\text{Bar}}=0$ so $S=1$ and $R=0$. If the clock is zero master is inactive, and slave is active. Therefore, the outputs of the slave will be $Q=1$ and $Q_{\text{Bar}}=0$. Hence, the outputs are $Q=1$ and $Q_{\text{Bar}}=0$. When $J=k=1$ the output toggles. If the clock is one Master is active, and slave is inactive, and the output of master are $Q1=1$ and $Q_{\text{bar}}=1$ and stays even when the clock is low because when the clock is 0 the master is inactive and the output of slave is not fed to the master. Therefore, the output toggles and avoid racing effect of the JK flip-flop.

Figure 3.30 shows the digital frequency divider with two JK flip-flops connected in series. The output of 1st JK flip-flop is given as input to the second flip-flop. The inputs of both flip-flops J and K are supplied with V_{DD} otherwise J and K are made HIGH. When the clock

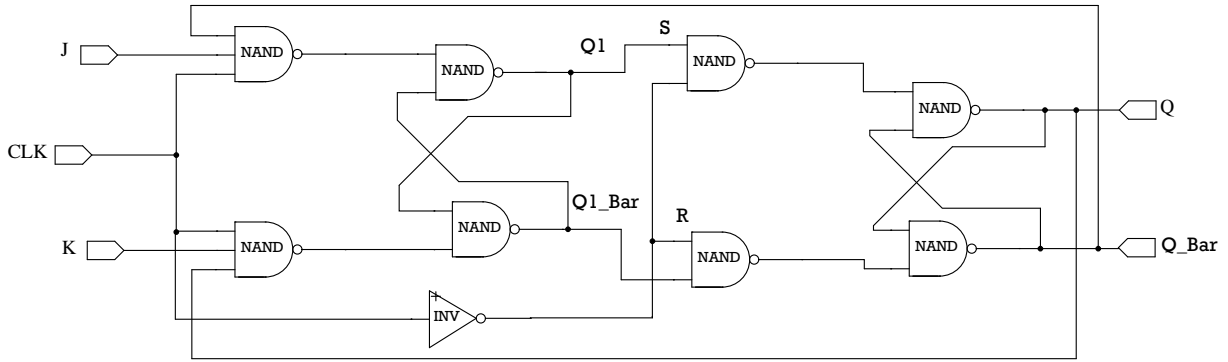


FIGURE 3.25. Schematic diagram of a JK Flip-Flop.

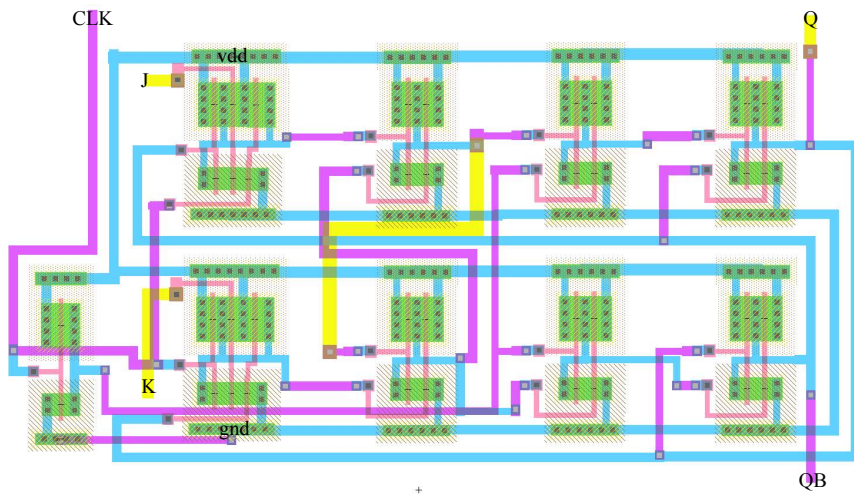


FIGURE 3.26. Layout Diagram of a JK Flip-Flop.

is given the output frequency of the 1st JK flip-flop at QA is a division of input frequency by 2. Similarly, the output frequency of 2nd JK flip-flop at QB is a division of input frequency by 4 (power-of-2 division). Figure 3.26 shows the layout diagram of a JK flip-flop. The layout area of the implemented JK flip-flop ALU is $189.9\mu\text{m} \times 347.0\mu\text{m}$.

3.3.1.2. NAND Gate

A NAND gate is formed with two PMOS transistors connected in parallel and two NMOS transistors connected in series. Figure 3.27 shows the schematic diagram of a NAND gate. The PMOS transistor's source is connected to V_{DD} and NMOS transistor's source is connected to ground. A and B are the inputs of the NAND gate, and ANANDB is the

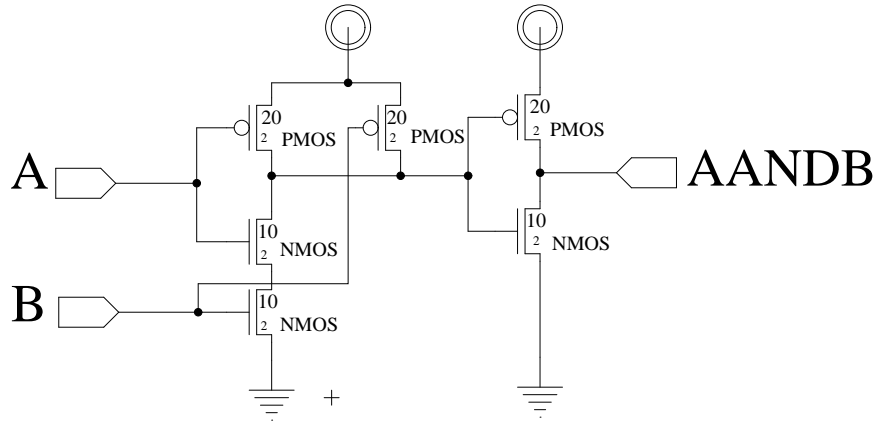


FIGURE 3.27. Schematic Diagram of NAND gate.

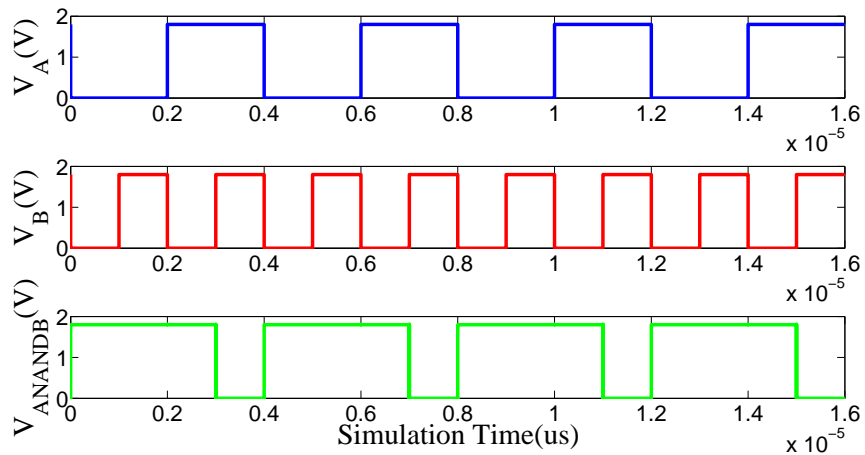


FIGURE 3.28. Simulation results for NAND gate.

output. When A and B are HIGH the output ANANDB is LOW, rest of all cases the output is HIGH. Figure 3.28 shows the simulation results for the NAND gate. Figure 3.29 shows the layout diagram of a NAND gate. Polysilicon-1 contact is used for input A and B, the metal-1 pin is used for output ANANDB. The layout area of the implemented NAND gate is $89.9\mu\text{m} \times 70.0\mu\text{m}$.

3.3.2. Implementation of Frequency divider

Figure 3.30 shows the schematic diagram of a frequency divider. It consists of two JK flip-flops connected in series. The clock is the input and QA, QB are the outputs of

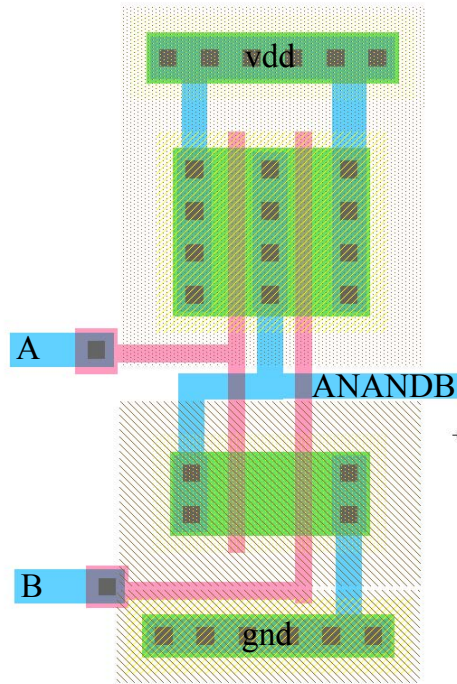


FIGURE 3.29. Layout Diagram of a NAND gate.

the frequency divider. The primary aim of the frequency divider is to divide the frequency of the signal which passes through it. The frequency divider implemented here divides the signal by power of two. The clock signal frequency is divided by 2, and the result is obtained at QA, and similarly, the input clock signal frequency is divided by four and the result is obtained at QB. Figure 3.32 shows the simulation results of a frequency divider. From the figure, the input clock frequency is 250 KHz and the output QA signal frequency is 125 KHz (divided by 2) and the output QB signal frequency is 62.5 KHz (divided by 4). Figure 3.31 shows the layout diagram of frequency divider, the inputs and outputs, polysilicon-1 contact, metal-1,2,3 contacts are used. All the connection are drawn using poly, metal-1,2,3 arcs. The layout area of the implemented frequency divider is $224.4\mu\text{m} \times 788.8\mu\text{m}$.

3.4. 1-Bit SRAM

Memory is an essential component of any computing platform. Its primary functions are sorting data, Instructions, application software, system software and also it stores the data and instructions during any application's or program's execution [19]. SRAM (static

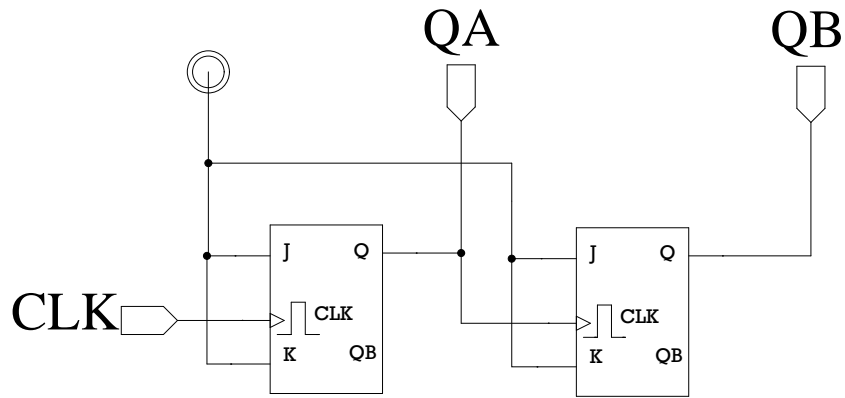


FIGURE 3.30. Schematic diagram of a Frequency divider.

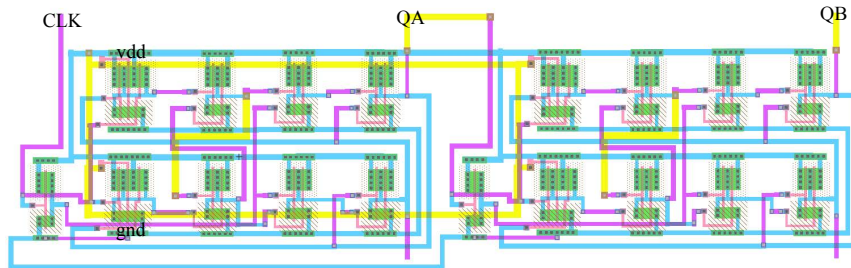


FIGURE 3.31. Layout diagram of a Frequency divider.

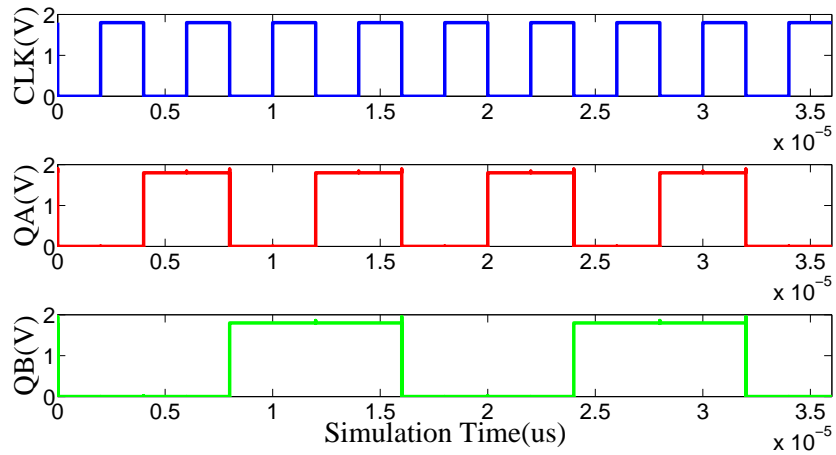


FIGURE 3.32. Simulation result for Frequency divider.

random access memory) is volatile memory and performs as a cache for processors. The word static means that it stores a bit electronically without needing periodic refreshing. It is a volatile memory, so it doesn't store data permanently, but it provides high-speed buffering

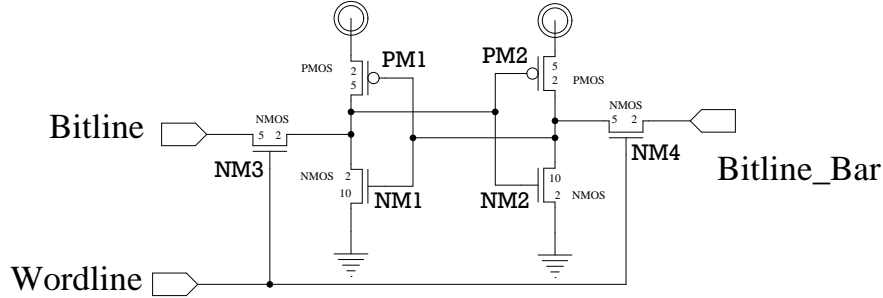


FIGURE 3.33. Schmatic circuit of an SRAM cell.

for processors. The term random access because any bit of data can be accessed at any time [2]. In this section, a 1-bit SRAM circuit is explained and designed in schematics and physical level.

3.4.1. 6T-Cell

The 6T-SRAM cell is the traditional SRAM cell which is widely used to build caches in computing systems. There are various types of SRAMs depending upon the clocking mechanism; they can be either asynchronous or synchronous SRAMs. 6T-SRAM is mainly preferable because it provides excellent results in the areas of stability, area, leakage power, and speed. Figure 3.33 shows the schematic diagram of 1-bit SRAM cell [31, 22]. The binary signal is stored in two cross-coupled inverters or a latch which is formed by four transistors. Two NMOS transistors are connected to the latch for reading and writing operations and are called access transistors. The six transistors are named drive transistors (NM1, NM2), load transistors (PM1, PM2) and access transistors (NM3, NM4). NM1, NM2 are sized wider than NM3, NM4 to achieve read stability. Similarly, NM1, NM2 are sized wider than PM1, PM2 for write stability. Figure 3.34 shows the layout diagram of a 6T-SRAM cell. The layout area of the implemented 6T-SRAM cell is $66.4\mu\text{m} \times 67.1\mu\text{m}$.

3.4.2. Implemtation of a 1-bit SRAM

The 1-bit SRAM array consists of a 6T-SRAM cell, a Sense-Amplifier, and a PRE-charge circuit [24]. The voltage across bit lines determines the bit stored in the SRAM cell. Whenever there is a large circuit of SRAM, getting proper output is difficult. Hence, the

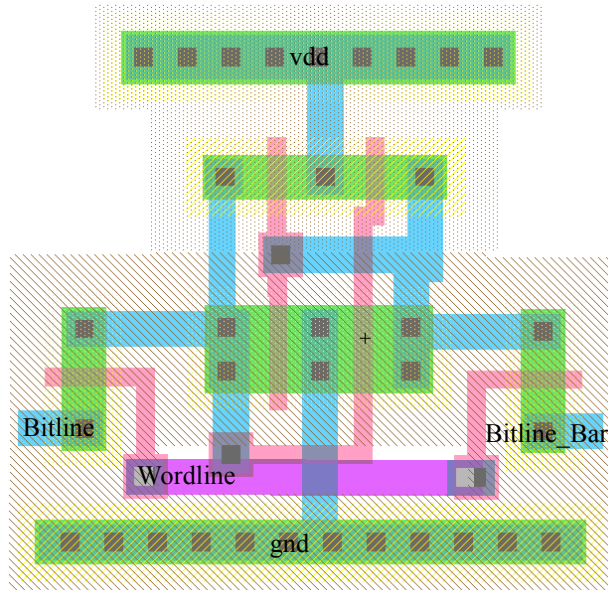


FIGURE 3.34. Layout diagram of an SRAM cell.

sense amplifier is used for reliability and stability to the circuitry. The main function of a sense amplifier is to sense the voltage across the bit lines and raise or lower the voltage levels. The pre-charge circuit is used to pre-charge the circuit to a voltage $V_{DD}/2$. Before every read and write operation, the pre-charge circuit is turned on to set the voltages of bit lines to $V_{DD}/2$, and then it is turned off. The sense amplifier is turned on, it senses the voltage difference and stores a bit in the SRAM cell. Figure 3.35 shows the schematic diagram of a 1-bit SRAM circuit. Figure 3.37 shows the waveforms of output. The Pre-charge circuit is turned on before the write operation. Logic 1 is given through Data_In signal. Sense amplifier and write enable (write) are turned HIGH at the same time, and then the word line (WL) is activated when all inputs are stable. Now, to read the logic 1 from the circuit, the Pre-charged circuit is re-activated and also Read enable (Read), sense amplifier and word line signals are activated again simultaneously. This activation of signals, makes Data_Out signal HIGH.

The operation of writing a zero is also similar to writing logic 1. The pre-charge circuit is turned on before writing zero. Then Data_In is made zero or low, sense amplifier and word lines are activated to store zero in SRAM cell. In a read operation, the zero

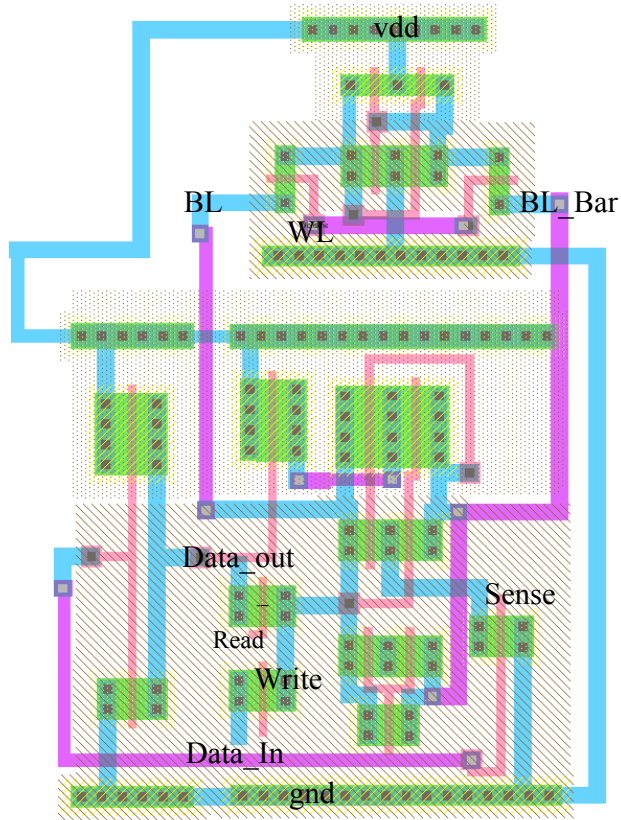


FIGURE 3.36. Layout diagram of an 1-bit SRAM.

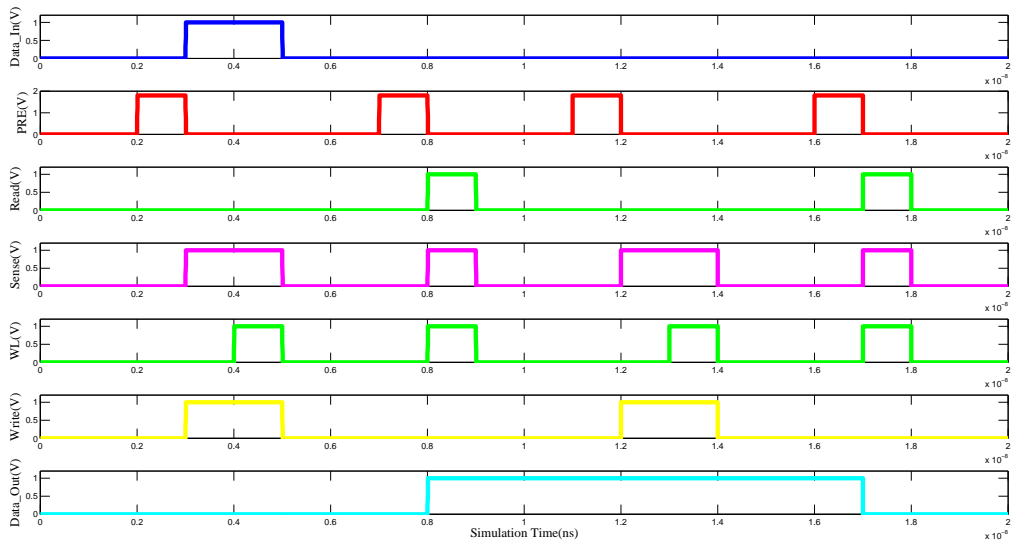


FIGURE 3.37. 1-Bit SRAM Timing Waveform.

CHAPTER 4

ANALOG INTEGRATED CIRCUIT DESIGN USING ELECTRIC

4.1. 3-Stage Ring Oscillator

The ring oscillator is an electronic device where an odd number of inverters are connected in a cascade manner and whose output varies or oscillates over two voltage levels representing true or false [2, 19]. Ring oscillators are widely used because they are very easy to design not only in CMOS technology but also in BiCMOS. They can be used in many applications in communication systems because of their ability to provide multiphase outputs when required. The other useful features of the ring oscillators are that it is possible to tune electrically and with low power, higher frequencies are also obtained [17]. The frequency of oscillation F_{osc} is given by the formula:

$$(1) \quad F_{osc} = \frac{1}{n(t_{PHL} + t_{PLH})},$$

where n = number of stages, t_{PHL} = propagation delay of a signal from High to low, and t_{PLH} = propagation delay of a signal from low to High. There are capacitances which are parasitics in the MOSFETS. So the total capacitance is given by $C_{tot} = C_{in} + C_{out}$ where $C_{in} = \frac{3}{2}(W_n L_n + W_p L_p)C_{ox}$ and $C_{out} = (W_n L_n + W_p L_p)C_{ox}$. The total capacitance is given by the formula.

$$(2) \quad C_{tot} = \frac{5}{2}(W_n L_n + W_p L_p)C_{ox},$$

where C_{ox} is the capacitance of the oxide. W_n, L_n are the width and length of nmos respectively and W_p, L_p are the width and length of pmos respectively. R_n is the resistance of the n-channel and R_p is the resistance of the p-channel. The propagation delay for the oscillator is given as:

$$(3) \quad t_{PHL} + t_{PLH} = (R_n + R_p)C_{tot}$$

4.1.1. Schematic Design

Figure 4.1 shows the schematic diagram of the CMOS inverter based 3-stage ring oscillator [8]. The factors that change oscillation frequency of the ring oscillator are propagation delay t_d of a stage and number of stages present in the closed chain loop. The propagation delay and number of stages are inversely proportional to oscillation frequency. Hence for higher frequencies the number of stages should be reduced which indirectly reduces the propagation delay. Reducing number of stages is important because it helps to have more area in the chips and reduces power consumption too. Here in this section a 3-stage ring oscillator is designed.

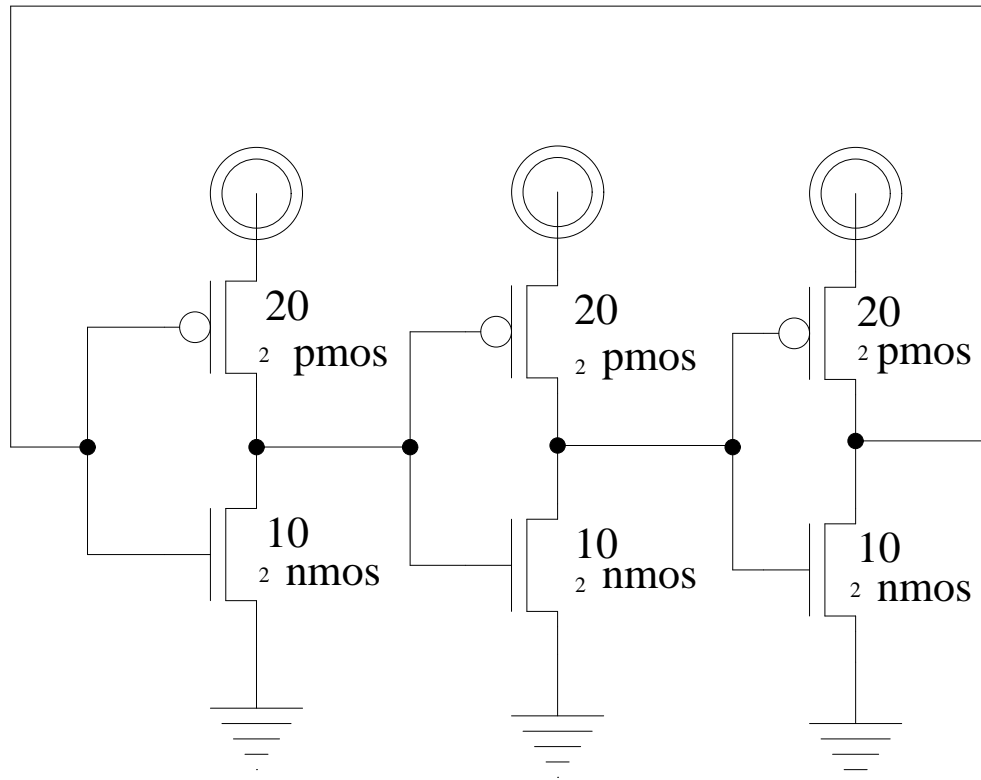


FIGURE 4.1. Schematic diagram of 3-Stage Ring Oscillator

If a square pulse with period T and frequency f_{clk} is given as an input to the inverter, the current that it must pull from V_{DD} is given as $I_{avg} = \frac{V_{DD}C_{tot}}{T}$ and the average power dissipation of an inverter is given by :

$$(4) \quad P_{avg} = V_{DD}I_{avg} = \frac{V_{DD}^2 C_{tot}}{T} = C_{tot}V_{DD}f_{clk}.$$

The power delay product (PDP) is often used to compare different technologies or device sizes; it characterizes the speed of a digital process and it is given by the relation:

$$(5) \quad PDF = P_{avg}(t_{PHL} + t_{PLH}).$$

4.1.2. Physical Design

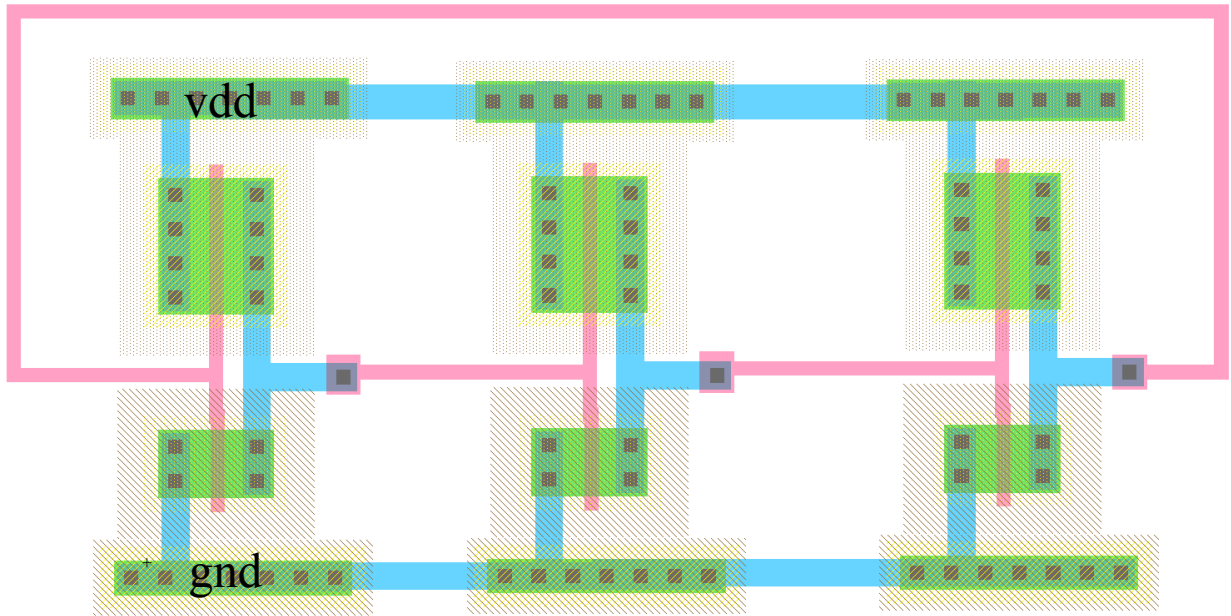


FIGURE 4.2. Layout Diagram of 3-Stage Ring Oscillator.

The physical design of the 3-stage ring oscillator is shown in figure 4.2. The layout is drawn as per the design rules of the 180nm TSMC CMOS technology. The Inverter library is used to design the 3-stage ring oscillator. For connections poly, metal-1 arcs are used and for contacts polysilicon-1 contact is used.

4.1.3. Simulation Results

Figure 4.3 shows the simulation results of the 3 stage Ring Oscillator. The obtained operating frequency is 4.4 GHz. The waveform is plotted between time and output voltage.

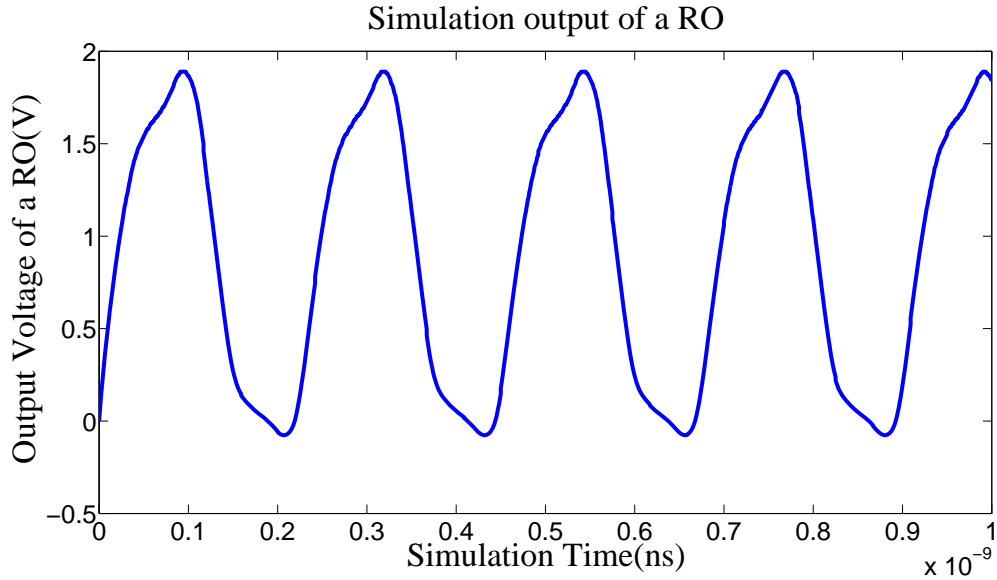


FIGURE 4.3. Simulation Result of a Ring Oscillator.

Ring Oscillator Characteristics	Specific Values
Technology	TSMC 180-nm CMOS
VDD	1.8V
Initial Voltage	0V
O/P Frequency	4.4 GHz
Average Power	41.34 μ Watts
C_{ox} Oxide capacitance	8.5fF
R_n effective resistance of n-channel MOSFET	3.2K Ω
R_p effective resistance of p-channel MOSFET	3.9K Ω

TABLE 4.1. Ring Oscillator Characteristics

4.2. Voltage Controlled Oscillator

The VCO is one of the central components in Phase Locked Loops (PLL), where it is widely used. A VCO has an odd number of inverters which is similar to Ring oscillator, but the propagation delays t_{PHL} and t_{PLH} of each inverter are controlled by the current source and current sink that are present above and below each inverter respectively [9, 19]. Input voltage controls the output frequency of a VCO.

The schematic diagram of a VCO is shown in figure 4.6. Two high impedance transistors M1 and M2 are present in the input stage of a VCO. Transistors M4 and M5 operates as an inverter in the current starved stage. The current source and sink transistor M3 and M6 limit the current flow to the inverters making them starve for the current [14]. The size of the transistors and number of inverters factors the oscillation frequency of a VCO.

4.2.1. Schematic Design

For the design equations of a VCO, consider a single inverter with transistors M4 and M5 shown in the figure 4.4. The capacitance of the inverter is given by $C_{tot} = C_{in} + C_{out}$ where $C_{in} = \frac{3}{2}(W_n L_n + W_p L_p)C_{ox}$ and $C_{out} = (W_n L_n + W_p L_p)C_{ox}$. The total capacitance of the inverter is given by:

$$(6) \quad C_{tot} = \frac{5}{2}(W_n L_n + W_p L_p)C_{ox},$$

where C_{ox} is the capacitance of the oxide and W_n, L_n are the width and length of nmos and W_p, L_p are the width and length of pmos respectively. The total time taken by the capacitance of an inverter to charge and discharge is given by:

$$(7) \quad T_{D,Stage} = \frac{C_{tot}V_{DD}}{I_D}.$$

Therefore the oscillation frequency of the VCO is given by:

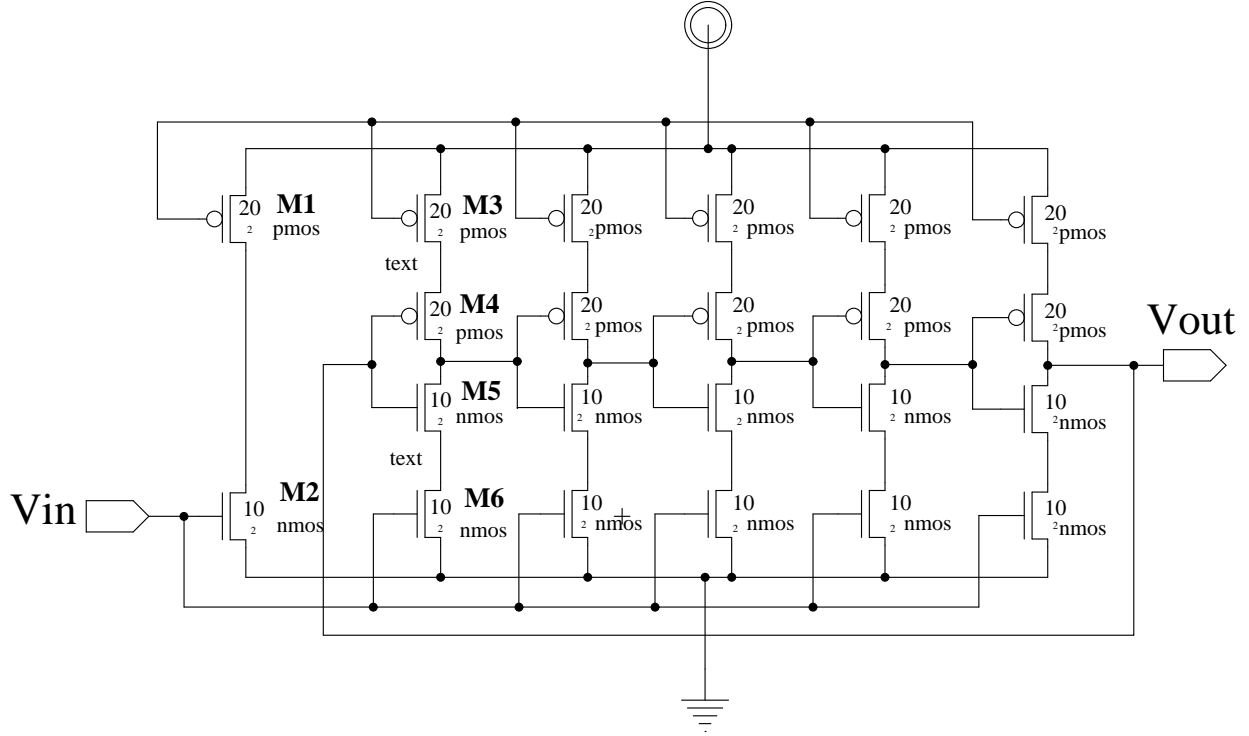


FIGURE 4.4. Schematic diagram of a 5-stage VCO.

$$(8) \quad F_{osc} = \frac{1}{NT_{D,Stage}} = \frac{I_D}{NC_{tot}VDD}$$

The average current drawn by the VCO is given by $I_{avg} = \frac{NV_{DD}C_{tot}}{T} = N(V_{DD})C_{tot}F_{osc}$.

The average power dissipated by the VCO is :

$$(9) \quad P_{avg} = (V_{DD})I_{avg}.$$

4.2.2. Physical Design

Figure 4.5 displays the physical design of the VCO. The V_{in} input is formed by using poly arc and V_{out} is formed with polysilicon-1 contact. The two series PMOS's are connected to two series NMOS's in series. This library is arrayed for four times to form five stage voltage controlled oscillator and the inverter library is also used here. The layout area of the implemented VCO is $91.4\mu\text{m} \times 183.4\mu\text{m}$.

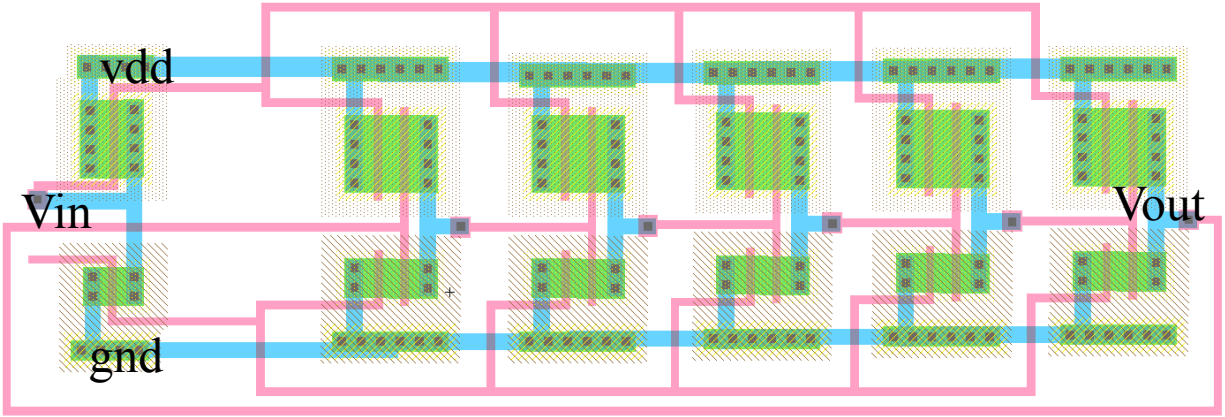


FIGURE 4.5. Layout Diagram of the a 5-Stage VCO.

4.2.3. Simulation results

Figure 4.6 shows the simulation results of the 5-stage VCO and table 4.2 shows the characteristics of the 5-stage VCO. The average power dissipated by is $180 \mu\text{W}$. The effective resistance of n-channel and p-channel MOSFETs are calculated using the TSMC 180 model file.

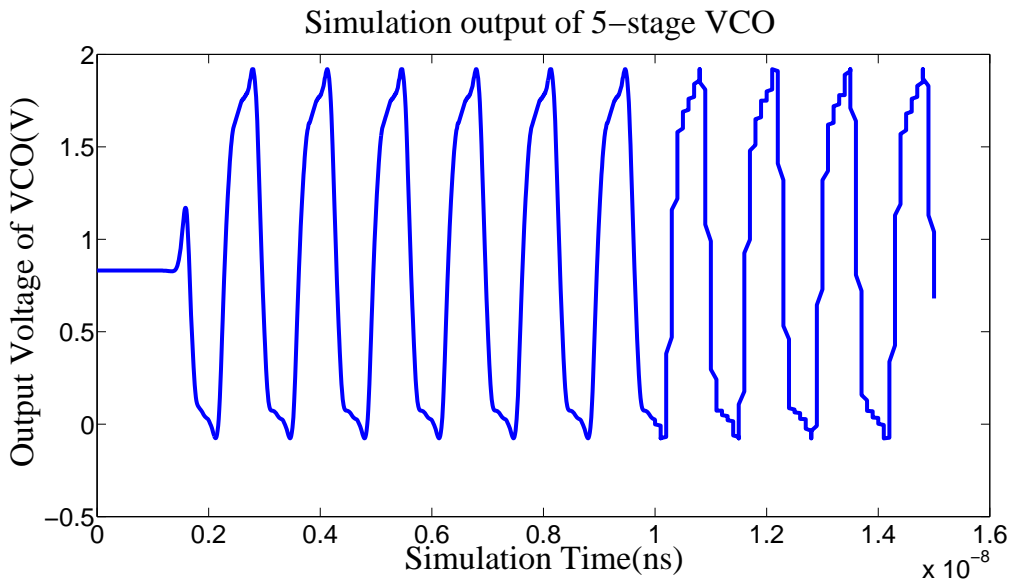


FIGURE 4.6. Simulation results for 5 stage VCO.

Voltage controlled Oscillator Characteristics	Specific Values
Technology	TSMC 180-nm CMOS
VDD	1.8V
Initial Voltage	0V
Average Power dissipated	180 μ Watts
C_{ox} Oxide capacitance	8.5fF
R_n effective resistance of n-channel MOSFET	3.2K Ω
R_p effective resistance of p-channel MOSFET	3.9K Ω

TABLE 4.2. Characteristics of the 180-nm TSMC CMOS VCO

4.3. Sense Amplifier

4.3.1. Schematic Design

The sense amplifier is one of the main components of memory circuits, and it is used to sense the bit lines for a 1 or 0 that was written to the cell. Figure 4.7 shows a full-latch cross-coupled sense amplifier that is fast and reliable [11]. The figure shows the schematic diagram of sense amplifier. The transistors (M4, M5, M6, M7) form a cross-coupled inverter, that is a primary component of a sense amplifier. M11, M10, M9 form a Precharge circuit that precharges the bit lines B0 and B1 to $V_{DD}/2$ voltage. Transistors M1 and M2 are called access transistors that are connected to memory cells, and the transistor M3 and M8 are used as a switch to active and deactivate the sense amplifier [19].

The primary step for reading out a DRAM cell is to precharge the bit lines BL and BL_Bar to $\frac{V_{DD}}{2}$ voltage, which is done by turning on the PRE signal to high with $V_{DD}/2$ voltage. When the PRE signal is low, the bit line BL and BL_Bar have equal $V_{DD}/2$ voltages, and then a wordline WL is turned ON. That creates the voltage difference between both bit lines BL_Bar and BL where the BL_Bar has a higher voltage than that of BL when a logic 1 is read. The SE signal is raised high which makes the sense amplifier turn

on, the n-channel of the cross-coupled inverter pulls one of the bit line low, and p-channel of the cross-coupled inverter that is triggered with $SE1$ pulls one of the bit line high. The signal is then amplified and read as logic “1”. When the wordline is still high, the value is written to the memory cell [25].

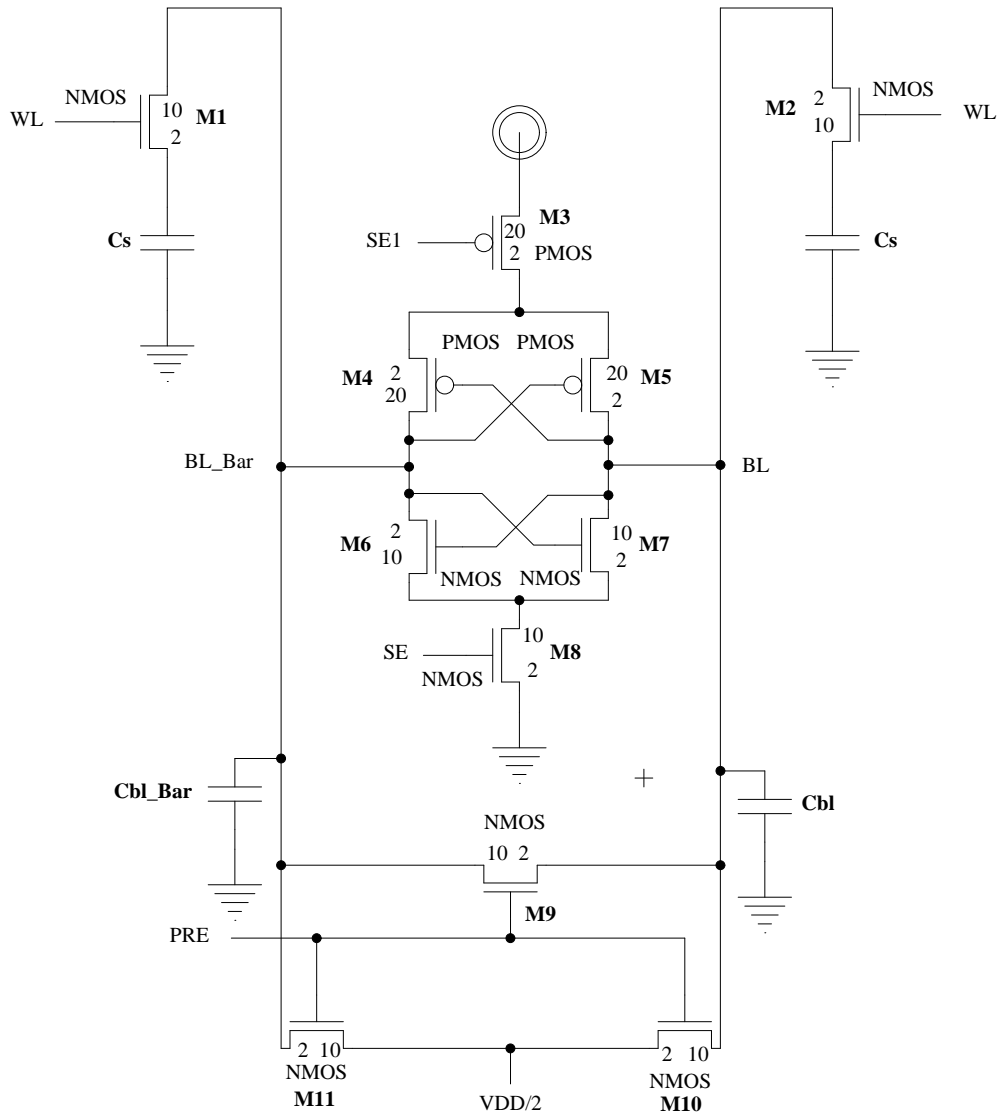


FIGURE 4.7. Schematic diagram of sense amplifier.

4.3.2. Physical Design

Figure 4.8 shows the layout design of a sense amplifier. For the input and outputs port, metal-1, polysilicon-1, metal-2 contacts are used and for connections polysilicon, metal-1,2 arcs are used. The layout area of the implemented sense amplifier is $125.3\mu\text{m} \times 89.1\mu\text{m}$.

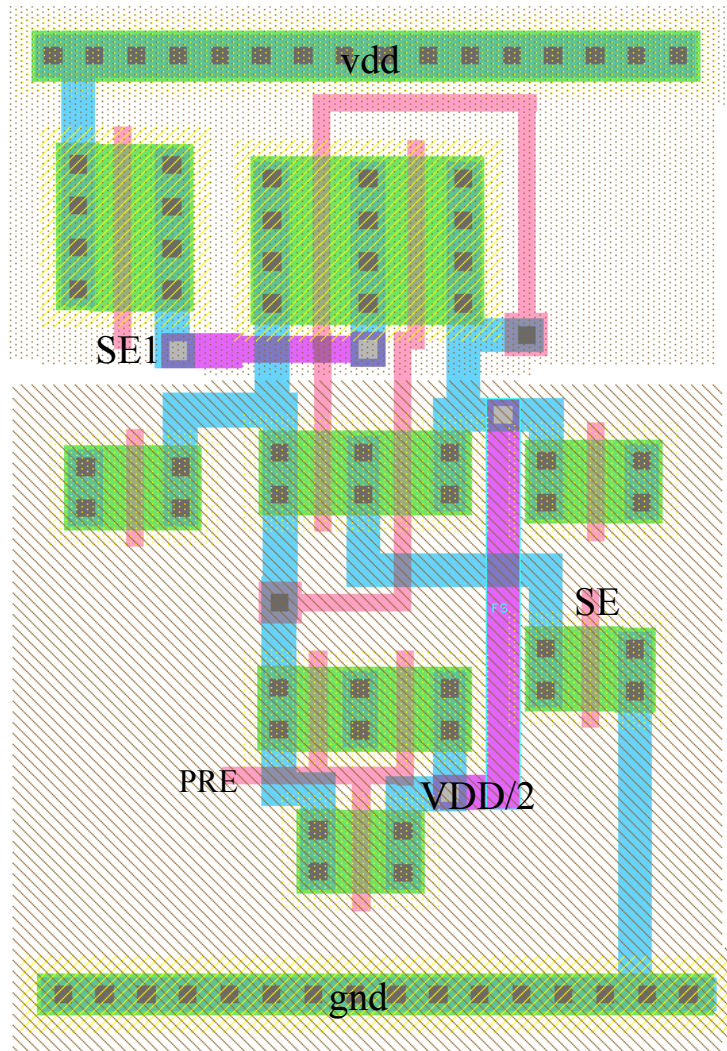


FIGURE 4.8. Physical design of sense amplifier.

4.3.3. Simulation Results

Figures 4.10 and 4.9 show the simulation results of the sense amplifier. Figure 4.9 is the sensing waveform, when the control signals 4.10 are applied to the circuit the Bl, and BL_bar show the results. At first, when the PRE charge signal is applied, both bit lines are

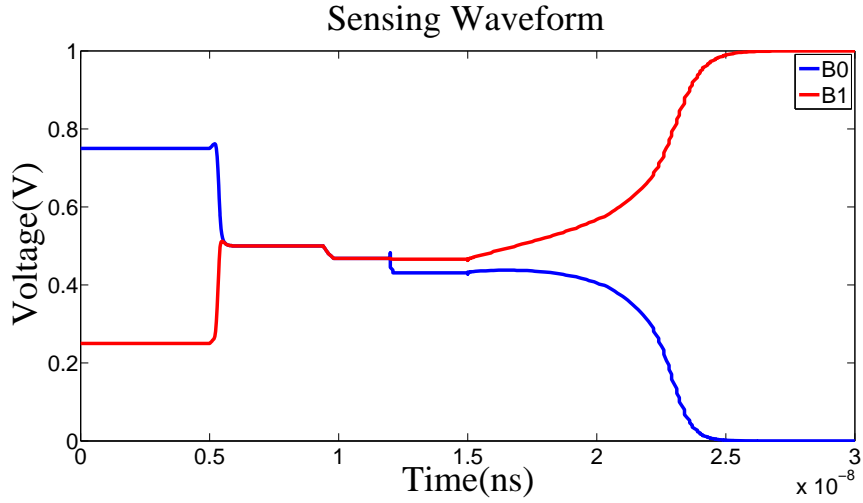


FIGURE 4.9. Sensing Waveform for sense amplifier.

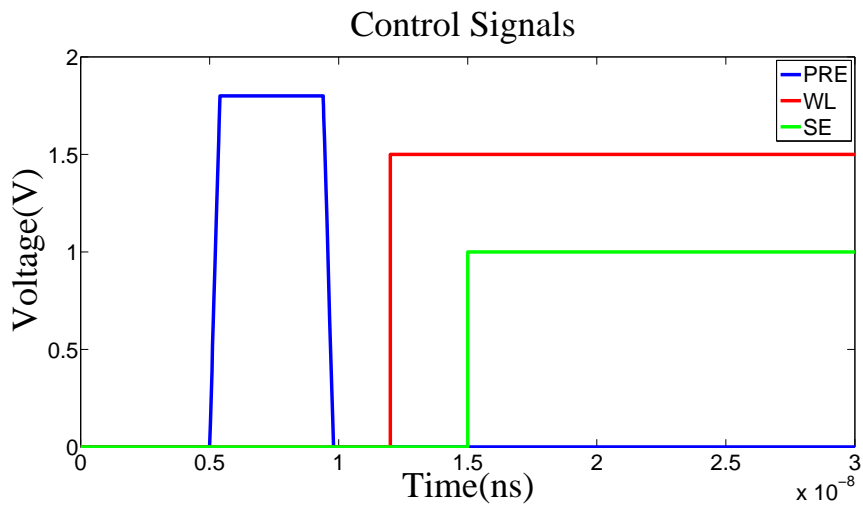


FIGURE 4.10. Control Signals for sense amplifier.

equalized to $V_{DD}/2$ voltage. Then when wordline is ON, the voltages vary in both bit lines. This voltage is observed by the sense amplifier when it is turned on. The sense amplifier amplifies the voltages of both bit lines. Here, in this case, the B0 is logic 0 and B1 is logic 1. Hence, the circuit accurately senses the signals.

4.4. Charge Pump

4.4.1. Schematic Design

A charge pump converts the digital signals from PFD to analog signals and supplies them to the VCO. It consists of two switches, a current source, and a current sink. Charge pumps are used in PLL's for a low-cost IC solution. They are also used in LCD drivers, voltage regulators, piezoelectric actuators, RF antenna switch controllers and many other electronic systems and their components [19, 15, 7].

A PLL has four important blocks: PFD, Charge pump, Loop Filter and VCO. The inputs UP and DOWN of the charge pump are the outputs of the PFD. These signals are regulated by the reference and feedback signals. When the reference signal leads the feedback signal, the PFD produces UP signal, and when feedback signal leads the reference signal, it provides DOWN signal [26]. The UP signal that is produced from the PFD will trigger the Charge pump to inject the charge into the loop filter, increasing the output voltage and likewise, when the DOWN signal is high, the Charge pump sinks the current out the loop filter, thus, the output voltage decreases [29]. If I_{CP} is the current of the charge pump the gain of the charge pump is given by:

$$(10) \quad K_{CP} = \frac{I_{CP}}{2\pi}$$

The current source and sink values should be the same to avoid current mismatching. Thus, VCO's control voltage is always the output voltage of charge pump. Figure 4.11 shows the schematic diagram of a charge pump.

4.4.2. Physical Design

Figure 4.13 shows the layout diagram of the charge pump. Polysilicon-1 contacts form the up and down input signals, and also the output signal Cpout. The layout area of the implemented sense amplifier is $121.3\mu\text{m} \times 144.8\mu\text{m}$.

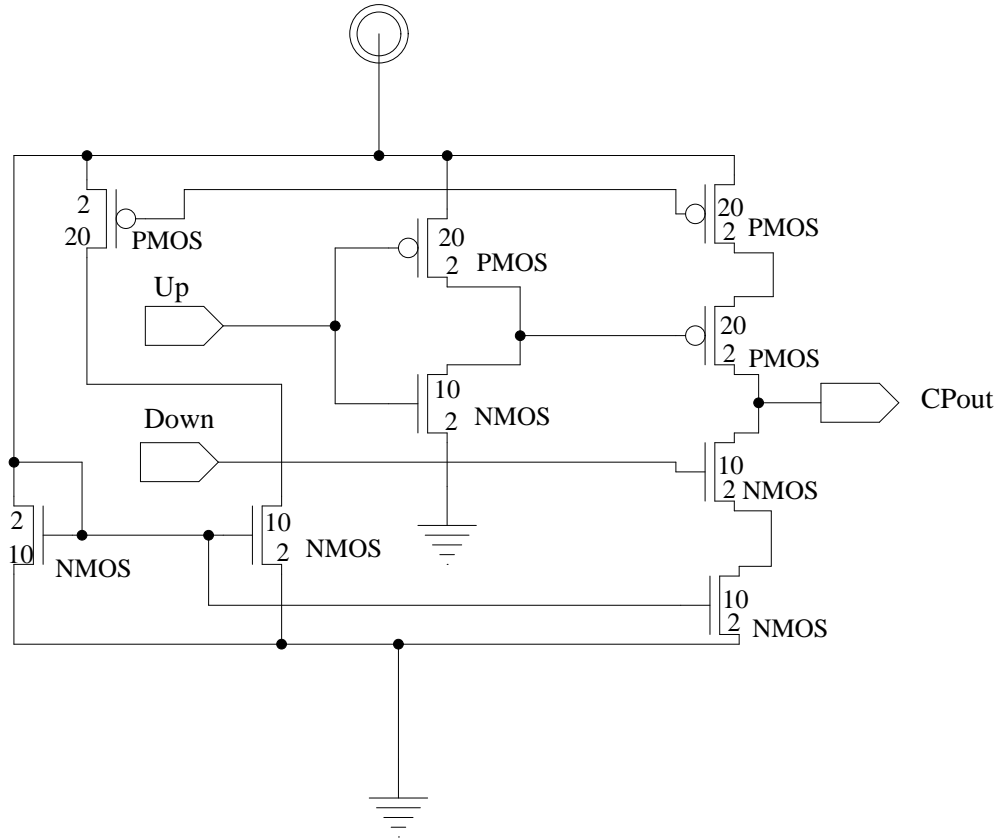


FIGURE 4.11. Schematic diagram of a Charge Pump.

4.4.3. Simulation Results

Figure 4.12 shows the simulation results of a charge pump circuit. When digital input voltages are given through Up and Down, the circuit converts them into analog signals and are given through Cpout.

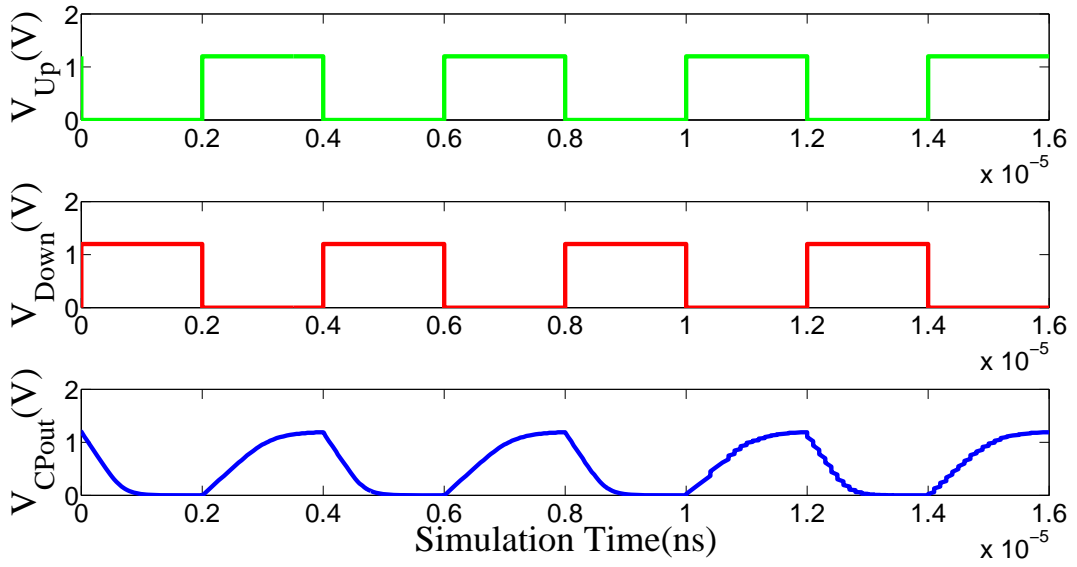


FIGURE 4.12. Simulation results for Charge Pump.

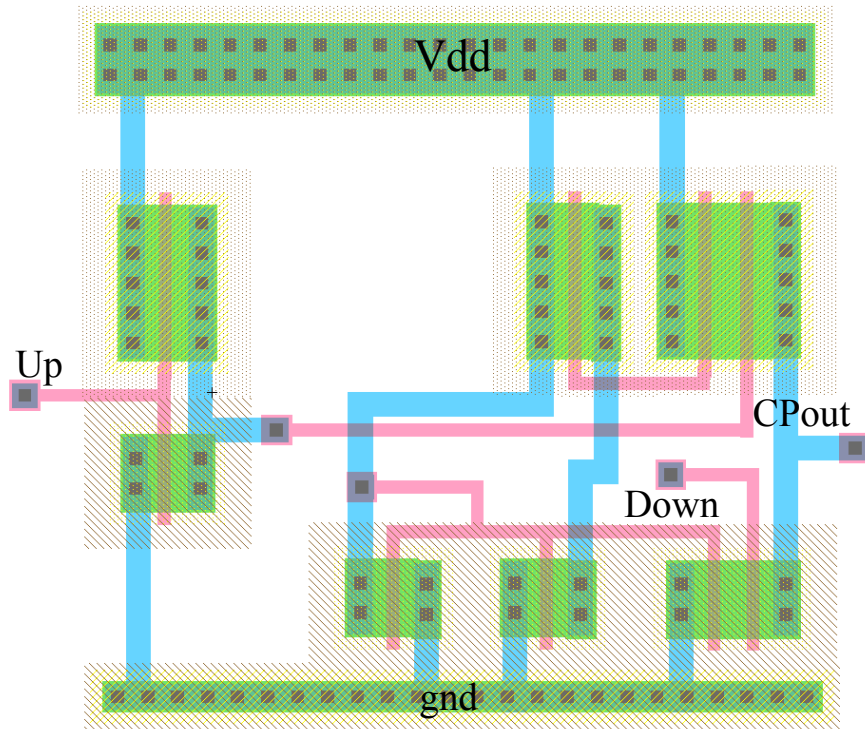


FIGURE 4.13. Physical design of charge pump.

CHAPTER 5

CONCLUSION AND FUTURE RESEARCH

5.1. Summary and Conclusions

The VLSI design course has become essential at most Electrical and Computer engineering programs. However, most of the commercial VLSI CAD systems are highly priced and require high-performance workstations which are not affordable for many academic institutions. This thesis provides some insight on the open-source EDA tool called Electric VLSI design system and serves as a user manual for students, teachers and other professionals who want to develop electric systems in affordable software.

The electric tool shows the best compatibility with all modern operating systems such as Windows, Macintosh, and UNIX/Linux variants. It also provides important analysis tools such as DRC (Design Rule Checker), Electric rule checker, Layout vs. Schematic checker and inbuilt simulators, IRSIM and ASL in a user-friendly interface. Synthesis tools are also built into electric which include Routers, placement tools, silicon compilers, and generators. Electric also provides an excellent way of integrating different environments of design. Since each fabrication process is enclosed in a technology in Electric, there are various technologies available in electric, but this thesis mainly concentrated on the CMOS technology. It also extracts the parasitics from the interconnects in the circuit designs. Electric can take python and java language scripts to design the circuit which automates the design cycle. It exports and imports many popular interchange and manufacturing formats such as EDIF, GDS-II, CIF, etc. The design flow for Digital and Analog circuits in electric is similar and very easy to learn for a student. The digital and analog design circuits are implemented in electric, in CMOS TSMC 180nm technology in chapter 3 and chapter 4. These simulation results are accurately correct and also show that electric can easily handle even more complex digital and analog schematic and layout designs. These designs, which are implemented using electric, will serve as examples for student projects and also help in further study of electric.

However there are some limitations in electric. Firstly it is not capable of designing below 180 nm technology. Secondly, Electric has integrated IRSIM, which only supports digital simulation, and there is no inbuilt analog simulator. There are solutions for these limitations in electric itself. One can edit the current technology using the technology creation wizard in electric. However, it is a daunting and time-consuming process . LTspice, which is a free circuit simulator, can also be integrated with electric for analog circuit simulations, which can then overcome this limitation of electric. Because of these reasons, Electric VLSI design system is expected to be useful the students, teachers and professionals.

5.2. Future Research

As a next step of this research, the digital and analog designs will be implemented for GNR-FET. Recently a CAD environment for the design, analysis, and layout of CNFET (Carbon Nanotube Filed-Effect Transistor Circuits) [12] has been created by Steven Rubin, within electric. This is the first physical design tool for analysis and layout of CNFET circuits which has been integrated into electric. Electric is a very promising tool for physical designing and simulation. To further explore the capabilities of the layout designing provided by electric, designs will be implemented using GNR-FET.

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